Data Sheet: Technical Data

KV30P64M100SFA Rev. 6, 03/2021

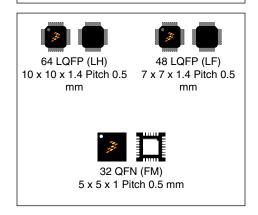
Kinetis KV30F 64 KB/128 KB Flash

100 MHz Arm® Cortex®-M4 Based Microcontroller with FPU

The KV30 MCU family is a highly scalable member of the Kinetis V series and provides a high-performance, cost-competitive motor-control solution. Built on the Arm® Cortex®-M4 core running at 100 MHz, combined with floating point and DSP capability, it delivers a highly capable platform enabling customers to build a highly scalable solution portfolio. Additional features include:

- Dual 16-bit ADCs sampling at up to 1.2 MS/s in 12-bit mode
- · Highly accurate and flexible motor control timers
- Excellent processing efficiency, 100 MHz Arm[®] Cortex[®]-M4-based device with Floating-Point Unit in a tiny form factor

MKV30F128Vxx10 MKV30F64Vxx10



Performance

 100 MHz Arm Cortex-M4 core with DSP instructions delivering 1.25 Dhrystone MIPS per MHz

Memories and memory interfaces

- Up to 128 KB of embedded flash and 16 KB of RAM
- Preprogrammed Kinetis flashloader for one-time, insystem factory programming

System peripherals

- 4-channel DMA controller
- · Independent External and Software Watchdog monitor

Clocks

- Crystal oscillator: 32-40 kHz or 3-32 MHz
- Three internal oscillators: 32 kHz, 4 MHz, and 48 MHz
- Multi-purpose clock generator with FLL

Security and integrity modules

- · Hardware CRC module
- 128-bit unique identification (ID) number per chip
- · Flash access control to protect proprietary software

Human-machine interface

• Up to 46 general-purpose I/O (GPIO)

Analog modules

- Two 16-bit SAR ADCs (1.2 MS/s in 12bit mode)
- One 12-bit DAC
- Two analog comparators (CMP) with 6- bit DAC
- Accurate internal voltage reference (not available in 32-pin QFN package)

Communication interfaces

- One SPI module
- Two UART modules
- One I2C: Support for up to 1 Mbps operation

Timers

- One 6-channel motor-control general-purpose/PWM timer
- Two 2-channel motor-control general-purpose timers with quadrature decoder functionality

Operating Characteristics

- Voltage range (including flash writes): 1.71 to 3.6 V
- Temperature range (ambient): -40 to 105°C



Ordering Information

Orderable Part Number	Part Number Marking	Memory Configuration	Package	Maximum number of I/O's
MKV30F128VLH10	MKV30F128VLH10	128 KB Flash16 SRAM	64 LQFP (10x10x1.6mm)	46
MKV30F128VLF10	M30J7V	128 KB Flash16 SRAM48 LQFP (7x7x1.6mm)		35
MKV30F128VFM10	M30J7V	128 KB Flash16 SRAM	32 QFN (5x5x0.9mm)	26
MKV30F64VLH10	MKV30F64VLH10	64 KB Flash16 SRAM	64 LQFP (10x10x1.6mm)	46
MKV30F64VLF10	M30J6V	64 KB Flash16 SRAM	48 LQFP (7x7x1.6mm)	35
MKV30F64VFM10	M30J6V	64 KB Flash16 SRAM	32 QFN (5x5x0.9mm)	26

Device Revision Number

Device Mask Set Number	SIM_SDID[REVID]	JTAG ID Register[PRN]		
0N36M	0000	0000		

Related Resources

Туре	Description	Resource
Selector Guide	The NXP Solution Advisor is a web-based tool that features interactive application wizards and a dynamic product selector.	Product Selector
Product Brief	The Product Brief contains concise overview/summary information to enable quick evaluation of a device for design suitability.	KV30FKV31FPB
Reference Manual	The Reference Manual contains a comprehensive description of the structure and function (operation) of a device.	KV30P64M100SFARM
Data Sheet	The Data Sheet includes electrical characteristics and signal connections.	This document.
Chip Errata	The chip mask set Errata provides additional or corrective information for a particular device mask set.	Kinetis_V_xN36M
Package drawing	Package dimensions are provided by the part number: • MKV30F128VLH10 • MKV30F128VLF10 • MKV30F128VFM10	98ASS23234W98ASH00962A98ARE10566D

Figure 1 shows the functional modules in the chip.

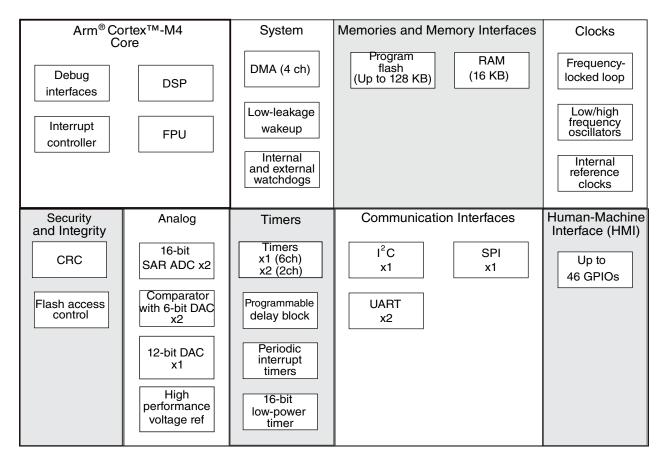


Figure 1. Functional block diagram

Table of Contents

1 Ra	tings5	3.6.1 ADC electrical specifications	30
1.1	Thermal handling ratings5	3.6.2 CMP and 6-bit DAC electrical specifications	34
1.2	Moisture handling ratings5	3.6.3 12-bit DAC electrical characteristics	37
1.3	ESD handling ratings5	3.6.4 Voltage reference electrical specifications	40
1.4	Voltage and current operating ratings5	3.7 Timers	41
2 Ge	neral6	3.8 Communication interfaces	41
2.1	AC electrical characteristics6	3.8.1 DSPI switching specifications (limited voltage	
2.2	Nonswitching electrical specifications6	range)	42
	2.2.1 Voltage and current operating requirements 6	3.8.2 DSPI switching specifications (full voltage	
	2.2.2 LVD and POR operating requirements7	range)	43
	2.2.3 Voltage and current operating behaviors8	3.8.3 Inter-Integrated Circuit Interface (I2C) timing	45
	2.2.4 Power mode transition operating behaviors 9	3.8.4 UART switching specifications	47
	2.2.5 Power consumption operating behaviors 10	4 Dimensions	47
	2.2.6 EMC radiated emissions operating behaviors16	4.1 Obtaining package dimensions	47
	2.2.7 Designing with radiated emissions in mind17	5 Pinout	47
	2.2.8 Capacitance attributes	5.1 KV30F Signal Multiplexing and Pin Assignments	47
2.3	Switching specifications	5.2 KV30F Signal Multiplexing and Pin Assignments	48
	2.3.1 Device clock specifications	5.3 Recommended connection for unused analog and	
	2.3.2 General switching specifications	digital pins	50
2.4	Thermal specifications	5.4 KV30F Pinouts	51
	2.4.1 Thermal operating requirements	5.5 KV30F Pinouts	52
	2.4.2 Thermal attributes	6 Part identification	55
3 Pe	ripheral operating requirements and behaviors20	6.1 Description	55
	Core modules	6.2 Format	55
	3.1.1 SWD electricals	6.3 Fields	56
	3.1.2 JTAG electricals	6.4 Example	56
3.2	System modules24	6.5 Package Markings	57
3.3	Clock modules	7 Terminology and guidelines	
	3.3.1 MCG specifications24	7.1 Definitions	
	3.3.2 IRC48M specifications26	7.2 Examples	
	3.3.3 Oscillator electrical specifications26	7.3 Typical-value conditions	
3.4	Memories and memory interfaces	7.4 Relationship between ratings and operating	
	3.4.1 Flash electrical specifications	requirements	59
3.5	Security and integrity modules	7.5 Guidelines for ratings and operating requirements	
	Analog	8 Revision History	

1 Ratings

1.1 Thermal handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
T _{STG}	Storage temperature	- 55	150	°C	1
T _{SDR}	Solder temperature, lead-free	_	260	°C	2

- 1. Determined according to JEDEC Standard JESD22-A103, High Temperature Storage Life.
- 2. Determined according to IPC/JEDEC Standard J-STD-020, Moisture/Reflow Sensitivity Classification for Nonhermetic Solid State Surface Mount Devices.

1.2 Moisture handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
MSL	Moisture sensitivity level	_	3	_	1

Determined according to IPC/JEDEC Standard J-STD-020, Moisture/Reflow Sensitivity Classification for Nonhermetic Solid State Surface Mount Devices.

1.3 ESD handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
V_{HBM}	Electrostatic discharge voltage, human body model	-2000	+2000	V	1
V _{CDM}	Electrostatic discharge voltage, charged-device model	-500	+500	V	2
I _{LAT}	Latch-up current at ambient temperature of 105°C	-100	+100	mA	3

- 1. Determined according to JEDEC Standard JESD22-A114, *Electrostatic Discharge (ESD) Sensitivity Testing Human Body Model (HBM)*.
- 2. Determined according to JEDEC Standard JESD22-C101, Field-Induced Charged-Device Model Test Method for Electrostatic-Discharge-Withstand Thresholds of Microelectronic Components.
- 3. Determined according to JEDEC Standard JESD78, IC Latch-Up Test.

1.4 Voltage and current operating ratings

Symbol	Description	Min.	Max.	Unit
V _{DD}	Digital supply voltage	-0.3	3.8	V
I _{DD}	Digital supply current	_	145	mA
V _{IN} ¹	Input voltage (except VBAT domain pins, and USB0)	-0.3	3.8	V
I _D	Maximum current single pin limit (digital output)	-25	25	mA
V_{DDA}	Analog supply voltage	- 0.3	3.8	V

^{1.} Includes ADC, CMP, and RESET_b inputs

2 General

2.1 AC electrical characteristics

Unless otherwise specified, propagation delays are measured from the 50% to the 50% point, and rise and fall times are measured at the 20% and 80% points, as shown in the following figure.

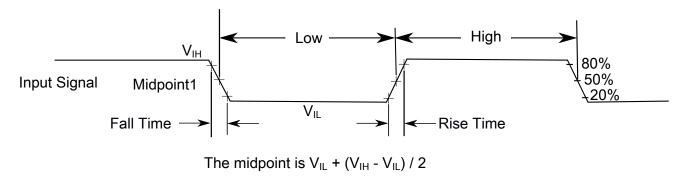


Figure 2. Input signal measurement reference

2.2 Nonswitching electrical specifications

2.2.1 Voltage and current operating requirements

Table 1. Voltage and current operating requirements

Symbol	Description	Min.	Max.	Unit	Notes
V _{DD}	Supply voltage	1.71	3.6	V	
V_{DDA}	Analog supply voltage	1.71	3.6	V	

Table 1. Voltage and current operating requirements (continued)

Symbol	Description	Min.	Max.	Unit	Notes
$V_{DD} - V_{DDA}$	V _{DD} -to-V _{DDA} differential voltage	-0.1	0.1	V	
V _{SS} – V _{SSA}	V _{SS} -to-V _{SSA} differential voltage	-0.1	0.1	V	
V _{BAT} :SR _{PWR}	Power Slew Rate	_	500	V/ms	1
V _{IH}	Input high voltage			V	
	• 2.7 V ≤ V _{DD} ≤ 3.6 V	$0.7 \times V_{DD}$	_	V	
	• 1.7 V ≤ V _{DD} ≤ 2.7 V	$0.75 \times V_{DD}$	_		
V _{IL}	Input low voltage	_	$0.35 \times V_{DD}$	V	
	• 2.7 V ≤ V _{DD} ≤ 3.6 V	_	$0.3 \times V_{DD}$	V	
	• 1.7 V ≤ V _{DD} ≤ 2.7 V				
V _{HYS}	Input hysteresis	0.06 × V _{DD}	_	V	
I _{ICIO}	Analog and I/O pin DC injection current — single pin				2
	V _{IN} < V _{SS} -0.3V (Negative current injection)	-3	_	mA	
I _{ICcont}	Contiguous pin DC injection current —regional limit, includes sum of negative injection currents or sum of positive injection currents of 16 contiguous pins				
	Negative current injection	-25	_	mA	
V _{ODPU}	Open drain pullup voltage level	V _{DD}	V_{DD}	V	3
V_{RAM}	V _{DD} voltage required to retain RAM	1.2	_	V	

^{1.} Applies to all voltages. Slew rate starts at 0 V

2.2.2 LVD and POR operating requirements

Table 2. V_{DD} supply LVD and POR operating requirements

Symbol	Description	Min.	Тур.	Max.	Unit	Notes
V _{POR}	Falling VDD POR detect voltage	0.8	1.1	1.5	V	
V _{LVDH}	Falling low-voltage detect threshold — high range (LVDV=01)	2.48	2.56	2.64	V	
	Low-voltage warning thresholds — high range					1
V _{LVW1H}	Level 1 falling (LVWV=00)	2.62	2.70	2.78	V	
V_{LVW2H}	Level 2 falling (LVWV=01)	2.72	2.80	2.88	V	
V _{LVW3H}	Level 3 falling (LVWV=10)	2.82	2.90	2.98	V	
V _{LVW4H}	Level 4 falling (LVWV=11)	2.92	3.00	3.08	V	

^{2.} All analog and I/O pins are internally clamped to V_{SS} through ESD protection diodes. If V_{IN} is less than -0.3 V, a current limiting resistor is required. The negative DC injection current limiting resistor is calculated as R=-0.3V/II_{ICIO}I. The actual resistor value should be an order of magnitude higher to tolerate transient voltages.

^{3.} Open drain outputs must be pulled to VDD.

Table 2. V_{DD} supply LVD and POR operating requirements (continued)

Symbol	Description	Min.	Тур.	Max.	Unit	Notes
V _{HYSH}	Low-voltage inhibit reset/recover hysteresis — high range	_	80	_	mV	
V _{LVDL}	Falling low-voltage detect threshold — low range (LVDV=00)	1.54	1.60	1.66	V	
	Low-voltage warning thresholds — low range					1
V _{LVW1L}	Level 1 falling (LVWV=00)	1.74	1.80	1.86	V	
V _{LVW2L}	Level 2 falling (LVWV=01)	1.84	1.90	1.96	V	
V _{LVW3L}	Level 3 falling (LVWV=10)	1.94	2.00	2.06	V	
V_{LVW4L}	Level 4 falling (LVWV=11)	2.04	2.10	2.16	V	
V _{HYSL}	Low-voltage inhibit reset/recover hysteresis — low range	_	60	_	mV	
V_{BG}	Bandgap voltage reference	0.97	1.00	1.03	V	
t _{LPO}	Internal low power oscillator period — factory trimmed	900	1000	1100	μs	

^{1.} Rising threshold is the sum of falling threshold and hysteresis voltage.

2.2.3 Voltage and current operating behaviors

Table 3. Voltage and current operating behaviors

Symbol	Description	Min.	Тур.	Max.	Unit	Notes
V _{OH}	Output high voltage — Normal drive pad except RESET_B					
	$2.7 \text{ V} \le \text{V}_{DD} \le 3.6 \text{ V}, \text{I}_{OH} = -5 \text{ mA}$	V _{DD} – 0.5	_	_	V	1
	$1.71 \text{ V} \le \text{V}_{DD} \le 2.7 \text{ V}, \text{I}_{OH} = -2.5 \text{ mA}$	V _{DD} – 0.5	_	_	V	
V _{OH}	Output high voltage — High drive pad except RESET_B					
	$2.7 \text{ V} \le \text{V}_{DD} \le 3.6 \text{ V}, \text{I}_{OH} = -20 \text{ mA}$	V _{DD} – 0.5	_	_	V	1
	$1.71 \text{ V} \le \text{V}_{DD} \le 2.7 \text{ V}, \text{I}_{OH} = -10 \text{ mA}$	V _{DD} – 0.5	_	_	V	
I _{OHT}	Output high current total for all ports	_	_	100	mA	
V _{OL}	Output low voltage — Normal drive pad except RESET_B					
	$2.7 \text{ V} \le \text{V}_{DD} \le 3.6 \text{ V}, \text{I}_{OL} = 5 \text{ mA}$	_	_	0.5	V	1
	$1.71 \text{ V} \le \text{V}_{DD} \le 2.7 \text{ V}, \text{I}_{OL} = 2.5 \text{ mA}$	_	_	0.5	V	
V _{OL}	Output low voltage — High drive pad except RESET_B					
	$2.7 \text{ V} \le \text{V}_{DD} \le 3.6 \text{ V}, \text{I}_{OL} = 20 \text{ mA}$	_	_	0.5	V	1
	$1.71 \text{ V} \le \text{V}_{DD} \le 2.7 \text{ V}, \text{I}_{OL} = 10 \text{ mA}$	_	_	0.5	V	
V _{OL}	Output low voltage — RESET_B					

Table 3. Voltage and current operating behaviors (continued)

Symbol	Description	Min.	Тур.	Max.	Unit	Notes
	$2.7 \text{ V} \le \text{V}_{DD} \le 3.6 \text{ V}, \text{I}_{OL} = 3 \text{ mA}$	_	_	0.5	V	
	$1.71 \text{ V} \le \text{V}_{DD} \le 2.7 \text{ V}, \text{I}_{OL} = 1.5 \text{ mA}$	_	_	0.5	V	
I _{OLT}	Output low current total for all ports	_	_	100	mA	
I _{IN}	Input leakage current (per pin) for full temperature range					
	All pins other than high drive port pins	_	0.002	0.5	μA	1, 2
	High drive port pins	_	0.004	0.5	μΑ	
I _{IN}	Input leakage current (total all pins) for full temperature range	_	_	1.0	μΑ	2
R _{PU}	Internal pullup resistors	20	_	50	kΩ	3
R _{PD}	Internal pulldown resistors	20	_	50	kΩ	4

- 1. PTB0, PTB1, PTC3, PTC4, PTD4, PTD5, PTD6, and PTD7 I/O have both high drive and normal drive capability selected by the associated PTx_PCRn[DSE] control bit. All other GPIOs are normal drive only.
- 2. Measured at VDD=3.6V
- 3. Measured at V_{DD} supply voltage = V_{DD} min and Vinput = V_{SS}
- 4. Measured at V_{DD} supply voltage = V_{DD} min and Vinput = V_{DD}

2.2.4 Power mode transition operating behaviors

All specifications except t_{POR} , and VLLSx \rightarrow RUN recovery times in the following table assume this clock configuration:

- CPU and system clocks = 72 MHz
- Bus clock = 36 MHz
- Flash clock = 24 MHz
- MCG mode: FEI

Table 4. Power mode transition operating behaviors

Symbol	Description	Min.	Тур.	Max.	Unit	Notes
t _{POR}	After a POR event, amount of time from the point V_{DD} reaches 1.71 V to execution of the first instruction across the operating temperature range of the chip.	_	_	300	μs	1
	• VLLS0 → RUN	_	_	135	μs	
	• VLLS1 → RUN	_	_	135	μs	
	• VLLS2 → RUN	_	_	75	μs	

Table 4. Power mode transition operating behaviors (continued)

Symbol	Description	Min.	Тур.	Max.	Unit	Notes
	VLLS3 → RUN					
		_	_	75	μs	
	VLPS → RUN					
	VER GOTTION	_	_	5.7	μs	
	• STOP → RUN					
		_	_	5.7	μs	

^{1.} Normal boot (FTFA_OPT[LPBOOT]=1)

2.2.5 Power consumption operating behaviors

The current parameters in the table below are derived from code executing a while(1) loop from flash, unless otherwise noted.

The IDD typical values represent the statistical mean at 25°C, and the IDD maximum values for RUN, WAIT, VLPR, and VLPW represent data collected at 125°C junction temperature unless otherwise noted. The maximum values represent characterized results equivalent to the mean plus three times the standard deviation (mean + 3 sigma).

Table 5. Power consumption operating behaviors

Symbol	Description	Min.	Тур.	Max.	Unit	Notes
I _{DDA}	Analog supply current	_	_	See note	mA	1
I _{DD_HSRUN}	High Speed Run mode current - all peripheral clocks disabled, CoreMark benchmark code executing from flash					
	@ 1.8V	_	18.70	19.37	mA	2, 3, 4
	@ 3.0V	_	18.71	19.38	mA	
I _{DD_HSRUN}	High Speed Run mode current - all peripheral clocks disabled, code executing from flash					
	@ 1.8V	_	18.13	18.80	mA	4
	@ 3.0V	_	18.19	18.86	mA	
I _{DD_HSRUN}	High Speed Run mode current — all peripheral clocks enabled, code executing from flash					
	@ 1.8V	_	22.2	22.87	mA	5
	@ 3.0V	_	22.4	23.07	mA	
I _{DD_RUN}	Run mode current in Compute operation — CoreMark benchmark code executing from flash					
	@ 1.8V	_	12.74	13.41	mA	2, 3, 6
	@ 3.0V	_	12.82	13.49	mA	

Table 5. Power consumption operating behaviors (continued)

Symbol	Description	Min.	Тур.	Max.	Unit	Notes
I _{DD_RUN}	Run mode current in Compute operation — code executing from flash					
	@ 1.8V	_	12.10	13.10	mA	6
	@ 3.0V	_	12.20	13.37	mA	
I _{DD_RUN}	Run mode current — all peripheral clocks disabled, code executing from flash					
	@ 1.8V	_	12.8	13.47	mA	7
	@ 3.0V	_	12.9	13.57	mA	
I _{DD_RUN}	Run mode current — all peripheral clocks enabled, code executing from flash					
	@ 1.8V	_	14.8	15.47	mA	8
	@ 3.0V					
	• @ 25°C	_	14.9	15.57	mA	
	• @ 70°C	_	14.9	15.57	mA	
	• @ 85°C	_	14.9	15.57	mA	
	• @ 105°C	_	15.5	16.20	mA	
I _{DD_RUN}	Run mode current — Compute operation, code executing from flash					
	@ 1.8V	_	12.1	12.77	mA	9
	@ 3.0V					
	• @ 25°C	_	12.2	12.87	mA	
	• @ 70°C	_	12.2	12.87	mA	
	• @ 85°C	_	12.2	12.87	mA	
	• @ 105°C	_	12.7	13.37	mA	
I _{DD_WAIT}	Wait mode high frequency current at 3.0 V — all peripheral clocks disabled	_	5.5	6.17	mA	7
I _{DD_WAIT}	Wait mode reduced frequency current at 3.0 V — all peripheral clocks disabled	_	3.5	4.17	mA	10
I _{DD_VLPR}	Very-low-power run mode current in Compute operation — CoreMark benchmark code executing from flash					
	@ 1.8V	_	0.58	0.86	mA	2, 11, 3
	@ 3.0V	_	0.59	0.87	mA	
I _{DD_VLPR}	Very-low-power run mode current in Compute operation, code executing from flash					
	@ 1.8V	_	0.47	0.75	mA	11
	@ 3.0V	_	0.47	0.75	mA	
I _{DD_VLPR}	Very-low-power run mode current at 3.0 V — all peripheral clocks disabled	_	0.62	0.90	mA	12

Table 5. Power consumption operating behaviors (continued)

Symbol	Description	Min.	Тур.	Max.	Unit	Notes
I _{DD_VLPR}	Very-low-power run mode current at 3.0 V — all peripheral clocks enabled	_	0.76	1.04	mA	13
I _{DD_VLPW}	Very-low-power wait mode current at 3.0 V — all peripheral clocks disabled	_	0.28	0.56	mA	14
I _{DD_STOP}	Stop mode current at 3.0 V					
	@ -40°C to 25°C	_	0.26	0.33	mA	
	@ 70°C	_	0.30	0.47	mA	
	@ 85°C	_	0.35	0.52	mA	
	@ 105°C	_	0.43	0.60	mA	
I _{DD_VLPS}	Very-low-power stop mode current at 3.0 V					
	@ -40°C to 25°C	_	2.80	8.30	μΑ	
	@ 70°C	_	13.30	29.90	μΑ	
	@ 85°C	_	26.90	46.45	μΑ	
	@ 105°C	_	56.80	67.05	μΑ	
I _{DD_VLLS3}	Very low-leakage stop mode 3 current at 3.0 V					
	@ -40°C to 25°C	_	1.3	1.71	μΑ	
	@ 70°C	_	3.8	5.35	μΑ	
	@ 85°C	_	7.6	8.50	μΑ	
	@ 105°C	_	15.1	19.05	μΑ	
I _{DD_VLLS2}	Very low-leakage stop mode 2 current at 3.0 V					
	@ -40°C to 25°C	_	1.3	1.55	μΑ	
	@ 70°C	_	3.1	4.05	μΑ	
	@ 85°C	_	7.2	8.60	μΑ	
	@ 105°C	_	12.0	14.10	μΑ	
I _{DD_VLLS1}	Very low-leakage stop mode 1 current at 3.0 V					
	@ -40°C to 25°C	_	0.63	0.87	μΑ	
	@ 70°C	_	1.70	2.35	μΑ	
	@ 85°C	_	2.8	3.40	μΑ	
	@ 105°C	_	7.6	8.80	μΑ	
I _{DD_VLLS0}	Very low-leakage stop mode 0 current at 3.0 V with POR detect circuit enabled					
	@ -40°C to 25°C	_	0.35	0.46	μA	
	@ 70°C	_	1.38	1.94	μA	
	@ 85°C	_	2.4	2.95	μΑ	
	@ 105°C	_	7.3	8.45	μΑ	
I _{DD_VLLS0}	Very low-leakage stop mode 0 current at 3.0 V with POR detect circuit disabled					
	@ -40°C to 25°C	_	0.07	0.16	μΑ	
	@ 70°C	_	1.05	1.78	μΑ	
	@ 85°C		2.1	2.80	μA	

Table 5. Power consumption operating behaviors (continued)

Symbo	I Description	Min.	Тур.	Max.	Unit	Notes
	@ 105°C	_	6.9	8.25	μΑ	

- 1. The analog supply current is the sum of the active or disabled current for each of the analog modules on the device. See each module's specification for its supply current.
- 2. Cache on and prefetch on, low compiler optimization
- 3. CoreMark benchmark compiled using IAR 7.2 with optimization level low
- 100 MHz core and system clock, 50 MHz bus clock, and 25 MHz flash clock. MCG configured for FEE mode. All peripheral clocks disabled.
- 5. 100 MHz core and system clock, 50 MHz bus clock, and 25 MHz flash clock. MCG configured for FEI mode. All peripheral clocks enabled.
- 6. 72 MHz core and system clock, 36 MHz bus clock and 24 MHz flash clock. MCG configured for FEE mode. All peripheral clocks disabled. Compute operation.
- 7. 72 MHz core and system clock, 36 MHz bus clock, and 24 MHz flash clock. MCG configured for FEI mode. All peripheral clocks disabled.
- 8. 72 MHz core and system clock, 36 MHz bus clock, and 24 MHz flash clock. MCG configured for FEI mode. All peripheral clocks enabled.
- 72MHz core and system clock, 36MHz bus clock, and 24MHz flash clock. MCG configured for FEI mode. Compute operation.
- 10. 25 MHz core and system clock, 25 MHz bus clock, and 25 MHz flash clock. MCG configured for FEI mode.
- 11. 4 MHz core, system, and bus clock, and 1 MHz flash clock. MCG configured for BLPE mode. Compute operation. Code executing from flash.
- 12. 4 MHz core, system, and bus clock, and 1 MHz flash clock. MCG configured for BLPE mode. All peripheral clocks disabled. Code executing from flash.
- 13. 4 MHz core, system, and bus clock, and 1 MHz flash clock. MCG configured for BLPE mode. All peripheral clocks enabled, but peripherals are not in active operation. Code executing from flash.
- 14. 4 MHz core, system, and bus clock, and 1 MHz flash clock. MCG configured for BLPE mode. All peripheral clocks disabled.

Table 6. Low power mode peripheral adders—typical value

Symbol	Description		٦	Tempera	ature (°C	C)		Unit
		-40	25	50	70	85	105	
lirefsten4mHz	4 MHz internal reference clock (IRC) adder. Measured by entering STOP or VLPS mode with 4 MHz IRC enabled.	56	56	56	56	56	56	μΑ
l _{IREFSTEN32KHz}	32 kHz internal reference clock (IRC) adder. Measured by entering STOP mode with the 32 kHz IRC enabled.	52	52	52	52	52	52	μΑ
I _{EREFSTEN4MHz}	External 4 MHz crystal clock adder. Measured by entering STOP or VLPS mode with the crystal enabled.	206	228	237	245	251	258	uA
lerefsten32kHz	External 32 kHz crystal clock adder by means of the OSC0_CR[EREFSTEN and EREFSTEN] bits. Measured by entering all modes with the crystal enabled.							
	VLLS1	440	490	540	560	570	580	nA
	VLLS3	440	490	540	560	570	580	
	LLS	490	490	540	560	570	680	

Table 6. Low power mode peripheral adders—typical value (continued)

Symbol	Description		-	Tempera	ature (°C	C)		Unit
		-40	25	50	70	85	105	
	VLPS	510	560	560	560	610	680	
	STOP	510	560	560	560	610	680	
I _{48MIRC}	48 Mhz internal reference clock	350	350	350	350	350	350	μΑ
I _{CMP}	I _{CMP} CMP peripheral adder measured by placing the device in VLLS1 mode with CMP enabled using the 6-bit DAC and a single external input for compare. Includes 6-bit DAC power consumption.		22	22	22	22	22	μА
l _{UART}	UART peripheral adder measured by placing the device in STOP or VLPS mode with selected clock source waiting for RX data at 115200 baud rate. Includes selected clock source power consumption.							
	MCGIRCLK (4 MHz internal reference clock)	66	66	66	66	66	66	μA
	>OSCERCLK (4 MHz external crystal)	214	237	246	254	260	268	
I _{BG}	Bandgap adder when BGEN bit is set and device is placed in VLPx, LLS, or VLLSx mode.	45	45	45	45	45	45	μА
I _{ADC}	ADC peripheral adder combining the measured values at V _{DD} and V _{DDA} by placing the device in STOP or VLPS mode. ADC is configured for low power mode using the internal clock and continuous conversions.	42	42	42	42	42	42	μА

2.2.5.1 Diagram: Typical IDD_RUN operating behavior

The following data was measured under these conditions:

- MCG in FBE mode for 50 MHz and lower frequencies. MCG in FEE mode at frequencies between 50 MHz and 100MHz.
- No GPIOs toggled
- Code execution from flash with cache enabled
- For the ALLOFF curve, all peripheral clocks are disabled except FTFA

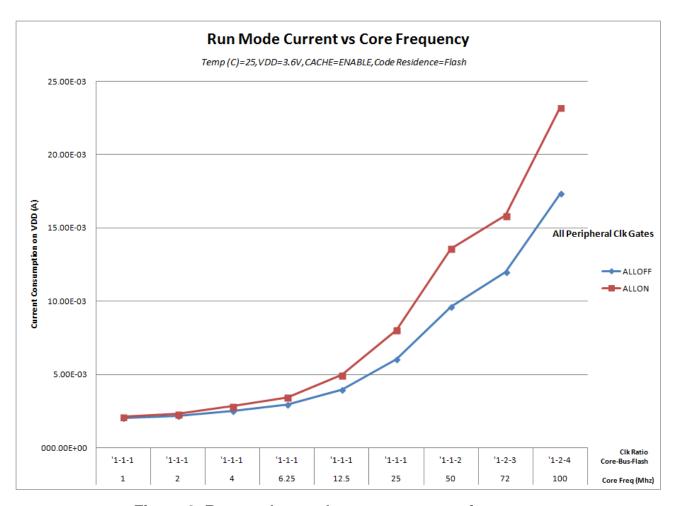


Figure 3. Run mode supply current vs. core frequency

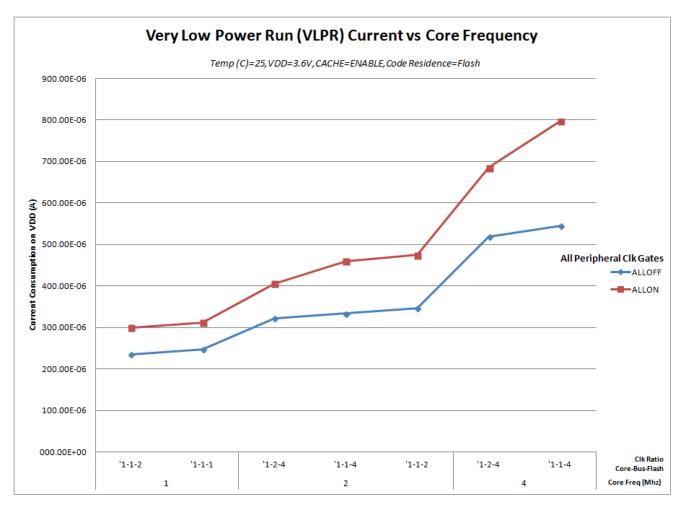


Figure 4. VLPR mode supply current vs. core frequency

2.2.6 EMC radiated emissions operating behaviors

Table 7. EMC radiated emissions operating behaviors for 64 LQFP package

Parame ter	Conditions	Clocks	Frequency range	Level (Typ.)	Unit	Notes
V_{EME}	Device configuration, test	FSYS = 100 MHz	150 kHz-50 MHz	11	dBuV	1, 2, 3
	conditions and EM testing per standard IEC	FBUS = 50 MHz	50 MHz-150 MHz	12		
	61967-2.	External crystal = 10 MHz	150 MHz-500 MHz	11		
	Supply voltage: VDD =		500 MHz-1000 MHz	8		
	3.3 V		IEC level	N		4
	Temp = 25°C					

- 1. Measurements were made per IEC 61967-2 while the device was running typical application code.
- 2. Measurements were performed on the 64LQFP device, MKV30F128VLH10.
- 3. The reported emission level is the value of the maximum measured emission, rounded up to the next whole number, from among the measured orientations in each frequency range.

4. IEC Level Maximums: $N \le 12dBmV$, $M \le 18dBmV$, $L \le 24dBmV$, $K \le 30dBmV$, $L \le 36dBmV$.

2.2.7 Designing with radiated emissions in mind

To find application notes that provide guidance on designing your system to minimize interference from radiated emissions:

- Go to nxp.com
- Perform a keyword search for "EMC design."

2.2.8 Capacitance attributes

Table 8. Capacitance attributes

Symbol	Description	Min.	Max.	Unit
C _{IN_A}	Input capacitance: analog pins	_	7	pF
C _{IN_D}	Input capacitance: digital pins	_	7	pF

2.3 Switching specifications

2.3.1 Device clock specifications

Table 9. Device clock specifications

Symbol	Description	Min.	Max.	Unit	Notes
	High Speed run mo	ode	•	•	•
f _{SYS}	System and core clock	_	100	MHz	
f _{BUS}	Bus clock	_	50	MHz	
	Normal run mode (and High Speed run mode ur	nless otherwi	se specified a	bove)	
f _{SYS}	System and core clock	_	72	MHz	
f _{BUS}	Bus clock	_	50	MHz	
f _{FLASH}	Flash clock	_	25	MHz	
f _{LPTMR}	LPTMR clock	_	25	MHz	
	VLPR mode ¹		•		
f _{SYS}	System and core clock	_	4	MHz	
f _{BUS}	Bus clock	_	4	MHz	
f _{FLASH}	Flash clock	_	1	MHz	
f _{ERCLK}	External reference clock	_	16	MHz	
f _{LPTMR_pin}	LPTMR clock	_	25	MHz	

Table 9. Device clock specifications (continued)

Symbol	Description	Min.	Max.	Unit	Notes
f _{LPTMR_ERCLK}	LPTMR external reference clock	_	16	MHz	

^{1.} The frequency limitations in VLPR mode here override any frequency specification listed in the timing specification for any other module.

2.3.2 General switching specifications

These general purpose specifications apply to all signals configured for GPIO, UART, and timers.

Table 10. General switching specifications

Symbol	Description	Min.	Max.	Unit	Notes
	GPIO pin interrupt pulse width (digital glitch filter disabled) — Synchronous path	1.5	_	Bus clock cycles	1, 2
	External RESET and NMI pin interrupt pulse width — Asynchronous path	100	_	ns	3
	GPIO pin interrupt pulse width (digital glitch filter disabled, passive filter disabled) — Asynchronous path	50	_	ns	4
	Port rise and fall time				5
	Slew disabled	_			
	• 1.71 ≤ V _{DD} ≤ 2.7V	_	10	ns	
	• 2.7 ≤ V _{DD} ≤ 3.6V		5	ns	
	Slew enabled	_			
	• 1.71 ≤ V _{DD} ≤ 2.7V	_	30	ns	
	• 2.7 ≤ V _{DD} ≤ 3.6V		16	ns	

^{1.} This is the minimum pulse width that is guaranteed to pass through the pin synchronization circuitry. Shorter pulses may or may not be recognized. In Stop, VLPS, LLS, and VLLSx modes, the synchronizer is bypassed so shorter pulses can be recognized in that case.

2.4 Thermal specifications

^{2.} The greater of synchronous and asynchronous timing must be met.

^{3.} These pins have a passive filter enabled on the inputs. This is the shortest pulse width that is guaranteed to be recognized.

^{4.} These pins do not have a passive filter on the inputs. This is the shortest pulse width that is guaranteed to be recognized.

^{5. 25} pF load

2.4.1 Thermal operating requirements

Table 11. Thermal operating requirements

Symbol	abol Description		Max.	Unit	Notes
TJ	Die junction temperature	-40	125	°C	
T _A	Ambient temperature	-40	105	°C	1

^{1.} Maximum T_A can be exceeded only if the user ensures that T_J does not exceed maximum T_J . The simplest method to determine T_J is: $T_J = T_A + R_{\Theta JA} \times$ chip power dissipation.

2.4.2 Thermal attributes

Board type	Symbol	Descriptio n	64 LQFP	48 LQFP	32 QFN	Unit	Notes
Single-layer (1s)	R _{eJA}	Thermal resistance, junction to ambient (natural convection)	66	79	97	°C/W	1
Four-layer (2s2p)	R _{θJA}	Thermal resistance, junction to ambient (natural convection)	48	55	33	°C/W	1
Single-layer (1s)	R _{елма}	Thermal resistance, junction to ambient (200 ft./min. air speed)	54	67	81	°C/W	1
Four-layer (2s2p)	R _{елма}	Thermal resistance, junction to ambient (200 ft./min. air speed)	41	49	28	°C/W	1
_	$R_{\theta JB}$	Thermal resistance, junction to board	30	33	13	°C/W	2
_	$R_{\theta JC}$	Thermal resistance, junction to case	17	23	2.0	°C/W	3
_	Ψ_{JT}	Thermal characterizati	3	5	6	°C/W	4

Board type	Symbol	Descriptio n	64 LQFP	48 LQFP	32 QFN	Unit	Notes
		on parameter, junction to package top outside center (natural convection)					

- 1. Determined according to JEDEC Standard JESD51-2, Integrated Circuits Thermal Test Method Environmental Conditions—Natural Convection (Still Air), or EIA/JEDEC Standard JESD51-6, Integrated Circuit Thermal Test Method Environmental Conditions—Forced Convection (Moving Air).
- 2. Determined according to JEDEC Standard JESD51-8, *Integrated Circuit Thermal Test Method Environmental Conditions—Junction-to-Board*.
- 3. Determined according to Method 1012.1 of MIL-STD 883, *Test Method Standard, Microcircuits*, with the cold plate temperature used for the case temperature. The value includes the thermal resistance of the interface material between the top of the package and the cold plate.
- 4. Determined according to JEDEC Standard JESD51-2, Integrated Circuits Thermal Test Method Environmental Conditions—Natural Convection (Still Air).

3 Peripheral operating requirements and behaviors

3.1 Core modules

3.1.1 SWD electricals

Table 12. SWD full voltage range electricals

Symbol	Description	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
S1	SWD_CLK frequency of operation			
	Serial wire debug	0	33	MHz
S2	SWD_CLK cycle period	1/S1	_	ns
S3	SWD_CLK clock pulse width			
	Serial wire debug	15	_	ns
S4	SWD_CLK rise and fall times	_	3	ns
S9	SWD_DIO input data setup time to SWD_CLK rise	8	_	ns
S10	SWD_DIO input data hold time after SWD_CLK rise	1.4	_	ns
S11	SWD_CLK high to SWD_DIO data valid	_	25	ns
S12	SWD_CLK high to SWD_DIO high-Z	5	_	ns

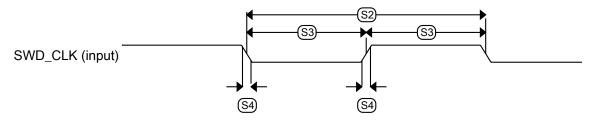


Figure 5. Serial wire clock input timing

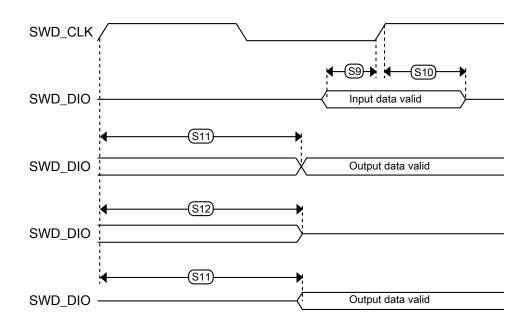


Figure 6. Serial wire data timing

3.1.2 JTAG electricals

Table 13. JTAG limited voltage range electricals

Symbol	Description	Min.	Max.	Unit
	Operating voltage	2.7	3.6	V
J1	J1 TCLK frequency of operation			MHz
	Boundary Scan	0	10	
	JTAG and CJTAG	0	20	
J2	TCLK cycle period	1/J1	_	ns
J3	TCLK clock pulse width			
		50	_	ns

Table 13. JTAG limited voltage range electricals (continued)

Symbol	Description	Min.	Max.	Unit
	Boundary Scan	25	_	ns
	JTAG and CJTAG			
J4	TCLK rise and fall times	_	3	ns
J5	Boundary scan input data setup time to TCLK rise	20	_	ns
J6	Boundary scan input data hold time after TCLK rise	1	_	ns
J7	TCLK low to boundary scan output data valid	_	25	ns
J8	TCLK low to boundary scan output high-Z	_	25	ns
J9	TMS, TDI input data setup time to TCLK rise	8	_	ns
J10	TMS, TDI input data hold time after TCLK rise	1	_	ns
J11	TCLK low to TDO data valid	_	19	ns
J12	TCLK low to TDO high-Z	_	19	ns
J13	TRST assert time	100	_	ns
J14	TRST setup time (negation) to TCLK high	8	_	ns

Table 14. JTAG full voltage range electricals

Symbol	Description	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
J1	TCLK frequency of operation			MHz
	Boundary Scan	0	10	
	JTAG and CJTAG	0	15	
J2	TCLK cycle period	1/J1	_	ns
J3	TCLK clock pulse width			
	Boundary Scan	50	_	ns
	JTAG and CJTAG	33	_	ns
J4	TCLK rise and fall times	_	3	ns
J5	Boundary scan input data setup time to TCLK rise	20	_	ns
J6	Boundary scan input data hold time after TCLK rise	1.4	_	ns
J7	TCLK low to boundary scan output data valid	_	27	ns
J8	TCLK low to boundary scan output high-Z	_	27	ns
J9	TMS, TDI input data setup time to TCLK rise	8	_	ns
J10	TMS, TDI input data hold time after TCLK rise	1.4	_	ns
J11	TCLK low to TDO data valid	_	26.2	ns
J12	TCLK low to TDO high-Z	_	26.2	ns
J13	TRST assert time	100	_	ns
J14	TRST setup time (negation) to TCLK high	8	_	ns

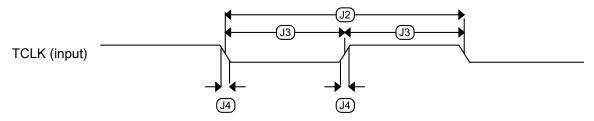


Figure 7. Test clock input timing

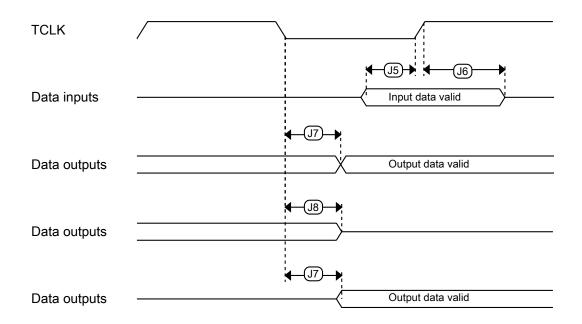


Figure 8. Boundary scan (JTAG) timing

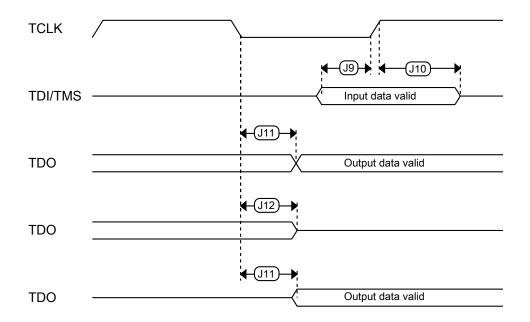


Figure 9. Test Access Port timing

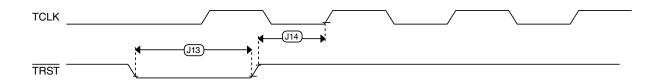


Figure 10. TRST timing

3.2 System modules

There are no specifications necessary for the device's system modules.

3.3 Clock modules

3.3.1 MCG specifications

Table 15. MCG specifications

Symbol	Description		Min.	Тур.	Max.	Unit	Notes
f _{ints_ft}		frequency (slow clock) — t nominal VDD and 25 °C	_	32.768	_	kHz	_
Δf_{ints_t}	Total deviation of (slow clock) over	_	+0.5/-0.7	± 2	%		
f _{ints_t}	Internal reference user trimmed	frequency (slow clock) —	31.25	_	39.0625	kHz	
$\Delta_{ ext{fdco_res_t}}$		med average DCO output voltage and temperature — d SCFTRIM	_	± 0.3	± 0.6	%f _{dco}	1
Δf_{dco_t}		trimmed average DCO output ltage and temperature	_	+0.5/-0.7	± 2	%f _{dco}	1, 2
Δf_{dco_t}	Total deviation of frequency over fix range of 0–70°C	_	± 0.3	± 1.5	%f _{dco}	1	
f _{intf_ft}	Internal reference factory trimmed a	_	4	_	MHz		
Δf_{intf_ft}	Frequency deviati (fast clock) over to factory trimmed a	_	+1/-2	± 5	%f _{intf_ft}		
f _{intf_t}	Internal reference frequency (fast clock) — user trimmed at nominal VDD and 25 °C		3	_	5	MHz	
f _{loc_low}	Loss of external clock minimum frequency — RANGE = 00		(3/5) x f _{ints_t}	_	_	kHz	
f _{loc_high}	Loss of external c RANGE = 01, 10,	lock minimum frequency — or 11	(16/5) x f _{ints_t}	_		kHz	
		FL	_L				
f _{fII_ref}	FLL reference free	quency range	31.25	_	39.0625	kHz	
f _{dco}	DCO output frequency range	Low range (DRS=00) $640 \times f_{\rm fll_ref}$	20	20.97	25	MHz	3, 4
		Mid range (DRS=01) $1280 \times f_{\rm fll_ref}$	40	41.94	50	MHz	
		Mid-high range (DRS=10) $1920 \times f_{\rm fil\ ref}$	60	62.91	75	MHz	
		High range (DRS=11) 2560 × f _{fll ref}	80	83.89	100	MHz	
dco_t_DMX3	DCO output frequency	Low range (DRS=00) $732 \times f_{fll_ref}$	_	23.99	_	MHz	5, 6
		Mid range (DRS=01) 1464 × f _{fll_ref}	_	47.97	_	MHz	
		Mid-high range (DRS=10)		71.99	_	MHz	

Symbol	Description	Description		Тур.	Max.	Unit	Notes
		2197 × f _{fll_ref}					
		High range (DRS=11)	_	95.98	_	MHz	
		2929 × f _{fll_ref}					
J _{cyc_fll}	FLL period jitter		_	_	_	ps	
	• f _{VCO} = 48 M	lHz	_	180	_		
	• f _{VCO} = 98 M	• f _{VCO} = 98 MHz		150			
t _{fll_acquire}	FLL target freque	ncy acquisition time	_	_	1	ms	7

- 1. This parameter is measured with the internal reference (slow clock) being used as a reference to the FLL (FEI clock mode).
- 2. 2.0 V <= VDD <= 3.6 V.
- 3. These typical values listed are with the slow internal reference clock (FEI) using factory trim and DMX32=0.
- The resulting system clock frequencies should not exceed their maximum specified values. The DCO frequency deviation (Δf_{dco t}) over voltage and temperature should be considered.
- 5. These typical values listed are with the slow internal reference clock (FEI) using factory trim and DMX32=1.
- 6. The resulting clock frequency must not exceed the maximum specified clock frequency of the device.
- 7. This specification applies to any time the FLL reference source or reference divider is changed, trim value is changed, DMX32 bit is changed, DRS bits are changed, or changing from FLL disabled (BLPE, BLPI) to FLL enabled (FEI, FEE, FBE, FBI). If a crystal/resonator is being used as the reference, this specification assumes it is already running.

3.3.2 IRC48M specifications

Table 16. IRC48M specifications

Symbol	Description	Min.	Тур.	Max.	Unit	Notes
V_{DD}	Supply voltage	1.71	_	3.6	V	
I _{DD48M}	Supply current	_	400	500	μΑ	
f _{irc48m}	Internal reference frequency — 48		_	MHz		
Δf _{irc48m_hv}	Total deviation of IRC48M frequency at high voltage (VDD=1.89V-3.6V) over full temperature	_	± 0.5	± 1.5	%f _{irc48m}	
Δf _{irc48m_hv}	Total deviation of IRC48M frequency at high voltage (VDD=1.89V-3.6V) over -40°C to 85°C	_	± 0.5	± 1.0	%f _{irc48m}	
Δf _{irc48m_lv}	Total deviation of IRC48M frequency at low voltage (VDD=1.71V-1.89V) over full temperature	_	± 0.5	± 2.0	%f _{irc48m}	
J _{cyc_irc48m}	Period Jitter (RMS)	_	35	150	ps	
t _{irc48mst}	Startup time	_	2	3	μs	1

- 1. IRC48M startup time is defined as the time between clock enablement and clock availability for system use. Enable the clock by one of the following settings:
 - MCG operating in an external clocking mode and MCG_C7[OSCSEL]=10 or MCG_C5[PLLCLKEN0]=1, or
 - SIM_SOPT2[PLLFLLSEL]=11

3.3.3 Oscillator electrical specifications

3.3.3.1 Oscillator DC electrical specifications Table 17. Oscillator DC electrical specifications

Symbol	Description	Min.	Тур.	Max.	Unit	Notes
V_{DD}	Supply voltage	1.71	_	3.6	V	
I _{DDOSC}	Supply current — low-power mode (HGO=0)					1
	• 32 kHz	_	500	_	nA	
	• 4 MHz	_	200	_	μA	
	• 8 MHz (RANGE=01)	_	300	_	μΑ	
	• 16 MHz	_	950	_	μA	
	• 24 MHz	_	1.2	_	mA	
	• 32 MHz	_	1.5	_	mA	
I _{DDOSC}	Supply current — high-gain mode (HGO=1)					1
	• 32 kHz	_	25	_	μA	
	• 4 MHz	_	400	_	μΑ	
	• 8 MHz (RANGE=01)	_	500	_	μΑ	
	• 16 MHz	_	2.5	_	mA	
	• 24 MHz	_	3	_	mA	
	• 32 MHz	_	4	_	mA	
C _x	EXTAL load capacitance	_	_	_		2, 3
Су	XTAL load capacitance	_	_	_		2, 3
R _F	Feedback resistor — low-frequency, low-power mode (HGO=0)	_	_	_	ΜΩ	2, 4
	Feedback resistor — low-frequency, high-gain mode (HGO=1)	_	10	_	ΜΩ	
	Feedback resistor — high-frequency, low-power mode (HGO=0)	_	_	_	ΜΩ	
	Feedback resistor — high-frequency, high-gain mode (HGO=1)	_	1	_	ΜΩ	
R _S	Series resistor — low-frequency, low-power mode (HGO=0)	_	_	_	kΩ	
	Series resistor — low-frequency, high-gain mode (HGO=1)	_	200	_	kΩ	
	Series resistor — high-frequency, low-power mode (HGO=0)	_	_	_	kΩ	
	Series resistor — high-frequency, high-gain mode (HGO=1)					
		_	0	_	kΩ	

Table 17. Oscillator DC electrical specifications (continued)

Symbol	Description	Min.	Тур.	Max.	Unit	Notes
V _{pp} ⁵	Peak-to-peak amplitude of oscillation (oscillator mode) — low-frequency, low-power mode (HGO=0)	_	0.6	_	V	
	Peak-to-peak amplitude of oscillation (oscillator mode) — low-frequency, high-gain mode (HGO=1)	_	V _{DD}	_	V	
	Peak-to-peak amplitude of oscillation (oscillator mode) — high-frequency, low-power mode (HGO=0)	_	0.6	_	V	
	Peak-to-peak amplitude of oscillation (oscillator mode) — high-frequency, high-gain mode (HGO=1)	_	V _{DD}	_	V	

- 1. V_{DD} =3.3 V, Temperature =25 °C
- 2. See crystal or resonator manufacturer's recommendation.
- 3. C_x and C_y can be provided by using either integrated capacitors or external components.
- 4. When low-power mode is selected, R_F is integrated and must not be attached externally.
- 5. The EXTAL and XTAL pins should only be connected to required oscillator components and must not be connected to any other device.

3.3.3.2 Oscillator frequency specifications Table 18. Oscillator frequency specifications

Symbol	Description	Min.	Тур.	Max.	Unit	Notes
f _{osc_lo}	Oscillator crystal or resonator frequency — low-frequency mode (MCG_C2[RANGE]=00)	32	_	40	kHz	
f _{osc_hi_1}	Oscillator crystal or resonator frequency — high-frequency mode (low range) (MCG_C2[RANGE]=01)	3	_	8	MHz	
f _{osc_hi_2}	Oscillator crystal or resonator frequency — high frequency mode (high range) (MCG_C2[RANGE]=1x)		_	32	MHz	
f _{ec_extal}	Input clock frequency (external clock mode)	_	_	50	MHz	1, 2
t _{dc_extal}	Input clock duty cycle (external clock mode)	40	50	60	%	
t _{cst}	Crystal startup time — 32 kHz low-frequency, low-power mode (HGO=0)	_	750	_	ms	3, 4
	Crystal startup time — 32 kHz low-frequency, high-gain mode (HGO=1)	_	250	_	ms	
	Crystal startup time — 8 MHz high-frequency (MCG_C2[RANGE]=01), low-power mode (HGO=0)	_	0.6	_	ms	
	Crystal startup time — 8 MHz high-frequency (MCG_C2[RANGE]=01), high-gain mode (HGO=1)	_	1	_	ms	

^{1.} Other frequency limits may apply when external clock is being used as a reference for the FLL

- 2. When transitioning from FEI or FBI to FBE mode, restrict the frequency of the input clock so that, when it is divided by FRDIV, it remains within the limits of the DCO input clock frequency.
- 3. Proper PC board layout procedures must be followed to achieve specifications.
- 4. Crystal startup time is defined as the time between the oscillator being enabled and the OSCINIT bit in the MCG_S register being set.

3.4 Memories and memory interfaces

3.4.1 Flash electrical specifications

This section describes the electrical characteristics of the flash memory module.

3.4.1.1 Flash timing specifications — program and erase

The following specifications represent the amount of time the internal charge pumps are active and do not include command overhead.

Table 19. NVM program/erase timing specifications

Symbol	bol Description		Тур.	Max.	Unit	Notes
t _{hvpgm4}	Longword Program high-voltage time	_	7.5	18	μs	_
t _{hversscr}	Sector Erase high-voltage time	_	13	113	ms	1
t _{hversall}	Erase All high-voltage time	_	104	904	ms	1

^{1.} Maximum time based on expectations at cycling end-of-life.

3.4.1.2 Flash timing specifications — commands Table 20. Flash command timing specifications

Symbol	Description	Min.	Тур.	Max.	Unit	Notes
t _{rd1sec2k}	Read 1s Section execution time (flash sector)	_	_	60	μs	1
t _{pgmchk}	Program Check execution time	_	_	45	μs	1
t _{rdrsrc}	Read Resource execution time	_	_	30	μs	1
t _{pgm4}	Program Longword execution time	_	65	145	μs	_
t _{ersscr}	Erase Flash Sector execution time	_	14	114	ms	2
t _{rd1all}	Read 1s All Blocks execution time	_	_	0.9	ms	1
t _{rdonce}	Read Once execution time	_	_	30	μs	1
t _{pgmonce}	Program Once execution time	_	100	_	μs	_
t _{ersall}	Erase All Blocks execution time	_	140	1150	ms	2
t _{vfykey}	Verify Backdoor Access Key execution time	_	_	30	μs	1

1. Assumes 25 MHz flash clock frequency.

2. Maximum times for erase parameters based on expectations at cycling end-of-life.

3.4.1.3 Flash high voltage current behaviors Table 21. Flash high voltage current behaviors

Symbol	Description	Min.	Тур.	Max.	Unit
I _{DD_PGM}	Average current adder during high voltage flash programming operation	_	2.5	6.0	mA
I _{DD_ERS}	Average current adder during high voltage flash erase operation	_	1.5	4.0	mA

3.4.1.4 Reliability specifications

Table 22. NVM reliability specifications

Symbol	Description	Min.	Typ. ¹	Max.	Unit	Notes		
	Program Flash							
t _{nvmretp10k}	Data retention after up to 10 K cycles	5	50	_	years	_		
t _{nvmretp1k}	Data retention after up to 1 K cycles	20	100	_	years	_		
n _{nvmcycp}	Cycling endurance	10 K	50 K	_	cycles	2		

Typical data retention values are based on measured response accelerated at high temperature and derated to a
constant 25 °C use profile. Engineering Bulletin EB618 does not apply to this technology. Typical endurance defined in
Engineering Bulletin EB619.

3.5 Security and integrity modules

There are no specifications necessary for the device's security and integrity modules.

3.6 Analog

3.6.1 ADC electrical specifications

The 16-bit accuracy specifications listed in Table 23 and Table 24 are achievable on the differential pins ADCx_DPx, ADCx_DMx.

All other ADC channels meet the 13-bit differential/12-bit single-ended accuracy specifications.

^{2.} Cycling endurance represents number of program/erase cycles at −40 °C ≤ T_i ≤ 125 °C.

3.6.1.1 16-bit ADC operating conditions Table 23. 16-bit ADC operating conditions

Symbol	Description	Conditions	Min.	Typ. ¹	Max.	Unit	Notes
V_{DDA}	Supply voltage	Absolute	1.71	_	3.6	V	
ΔV_{DDA}	Supply voltage	Delta to V _{DD} (V _{DD} – V _{DDA})	-100	0	+100	mV	2
ΔV_{SSA}	Ground voltage	Delta to V _{SS} (V _{SS} – V _{SSA})	-100	0	+100	mV	2
V_{REFH}	ADC reference voltage high		1.13	V_{DDA}	V_{DDA}	V	
V_{REFL}	ADC reference voltage low		V_{SSA}	V _{SSA}	V _{SSA}	V	
V_{ADIN}	Input voltage	16-bit differential mode	VREFL	_	31/32 * VREFH	V	
		All other modes	VREFL	_	VREFH		
C _{ADIN}	Input	16-bit mode	_	8	10	pF	
	capacitance	8-bit / 10-bit / 12-bit modes	_	4	5		
R _{ADIN}	Input series resistance		_	2	5	kΩ	
R _{AS}	Analog source resistance (external)	13-bit / 12-bit modes f _{ADCK} < 4 MHz	_	_	5	kΩ	3
f _{ADCK}	ADC conversion clock frequency	≤ 13-bit mode	1.0	_	24.0	MHz	4
f _{ADCK}	ADC conversion clock frequency	16-bit mode	2.0	_	12.0	MHz	4
C _{rate}	ADC conversion	≤ 13-bit modes					5
	rate	No ADC hardware averaging Continuous conversions enabled, subsequent conversion time	20	_	1200	Ksps	
C _{rate}	ADC conversion rate	16-bit mode No ADC hardware averaging Continuous conversions enabled, subsequent conversion time	37	_	461	Ksps	5

^{1.} Typical values assume $V_{DDA} = 3.0 \text{ V}$, Temp = 25 °C, $f_{ADCK} = 1.0 \text{ MHz}$, unless otherwise stated. Typical values are for reference only, and are not tested in production.

^{2.} DC potential difference.

^{3.} This resistance is external to MCU. To achieve the best results, the analog source resistance must be kept as low as possible. The results in this data sheet were derived from a system that had $< 8 \Omega$ analog source resistance. The R_{AS}/C_{AS} time constant should be kept to < 1 ns.

^{4.} To use the maximum ADC conversion clock frequency, CFG2[ADHSC] must be set and CFG1[ADLPC] must be clear.

^{5.} For guidelines and examples of conversion rate calculation, download the ADC calculator tool.

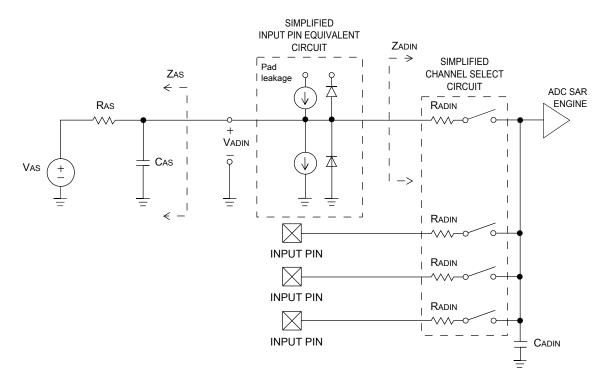


Figure 11. ADC input impedance equivalency diagram

3.6.1.2 16-bit ADC electrical characteristics

Table 24. 16-bit ADC characteristics ($V_{REFH} = V_{DDA}$, $V_{REFL} = V_{SSA}$)

Symbol	Description	Conditions ¹	Min.	Typ. ²	Max.	Unit	Notes		
I _{DDA_ADC}	Supply current		0.215	_	1.7	mA	3		
	ADC asynchronous	• ADLPC = 1, ADHSC = 0	1.2	2.4	3.9	MHz	t _{ADACK} = 1/		
_	clock source	• ADLPC = 1, ADHSC = 1	2.4	4.0	6.1	MHz	f _{ADACK}		
f _{ADACK}		• ADLPC = 0, ADHSC = 0	3.0	5.2	7.3	MHz			
		• ADLPC = 0, ADHSC = 1	4.4	6.2	9.5	MHz			
	Sample Time	See Reference Manual chapter for sample times							
TUE	Total unadjusted	12-bit modes	_	±4	±6.8	LSB ⁴	5		
	error	• <12-bit modes	_	±1.4	±2.1				
DNL	Differential non-	12-bit modes		±0.7	-1.1 to	LSB ⁴	5		
	linearity	• <12-bit modes	_	±0.2	+1.9 -0.3 to 0.5				
INL	Integral non-linearity	12-bit modes	_	±1.0	-2.7 to +1.9	LSB ⁴	5		

Table 24. 16-bit ADC characteristics ($V_{REFH} = V_{DDA}$, $V_{REFL} = V_{SSA}$) (continued)

Symbol	Description	Conditions ¹	Min.	Typ. ²	Max.	Unit	Notes
		• <12-bit modes	_	±0.5	-0.7 to +0.5		
E _{FS}	Full-scale error	12-bit modes	_	-4	-5.4	LSB ⁴	$V_{ADIN} = V_{DDA}^{5}$
		<12-bit modes	_	-1.4	-1.8		
EQ	Quantization error	16-bit modes	_	-1 to 0	_	LSB ⁴	
		• ≤13-bit modes	_	_	±0.5		
ENOB	Effective number of	16-bit differential mode					6
	bits	• Avg = 32	12.8	14.5	_	bits	
		• Avg = 4	11.9	13.8	_		
						bits	
		16-bit single-ended mode	12.2	13.9			
		• Avg = 32	11.4	13.1	_	bits	
		• Avg = 4			_	bits	
SINAD	Signal-to-noise plus distortion	See ENOB	6.02 ×	6.02 × ENOB + 1.76		dB	
THD	Total harmonic	16-bit differential mode				dB	7
	distortion	• Avg = 32	_	-94	_		
		4017				dB	
		16-bit single-ended mode	_	-85	_		
		• Avg = 32					
SFDR	Spurious free	16-bit differential mode	82	95	_	dB	7
	dynamic range	• Avg = 32	02	95	_	dB	
		16-bit single-ended mode	78	90		GD.	
		• Avg = 32	, ,				
		7.11g 0 <u>-</u>				.,,	
E _{IL}	Input leakage error			$I_{ln} \times R_{AS}$		mV	I _{In} = leakage current
							(refer to the MCU's voltage and current operating ratings)
	Temp sensor slope	Across the full temperature range of the device	1.55	1.62	1.69	mV/°C	8
V _{TEMP25}	Temp sensor voltage	25 °C	706	716	726	mV	8

^{1.} All accuracy numbers assume the ADC is calibrated with $V_{\text{REFH}} = V_{\text{DDA}}$

^{2.} Typical values assume $V_{DDA} = 3.0 \text{ V}$, Temp = 25 °C, $f_{ADCK} = 2.0 \text{ MHz}$ unless otherwise stated. Typical values are for reference only and are not tested in production.

^{3.} The ADC supply current depends on the ADC conversion clock speed, conversion rate and ADC_CFG1[ADLPC] (low power). For lowest power operation, ADC_CFG1[ADLPC] must be set, the ADC_CFG2[ADHSC] bit must be clear with 1 MHz ADC conversion clock speed.

Peripheral operating requirements and behaviors

- 4. $1 LSB = (V_{REFH} V_{REFL})/2^{N}$
- 5. ADC conversion clock < 16 MHz, Max hardware averaging (AVGE = %1, AVGS = %11)
- 6. Input data is 100 Hz sine wave. ADC conversion clock < 12 MHz.
- 7. Input data is 1 kHz sine wave. ADC conversion clock < 12 MHz.
- 8. ADC conversion clock < 3 MHz

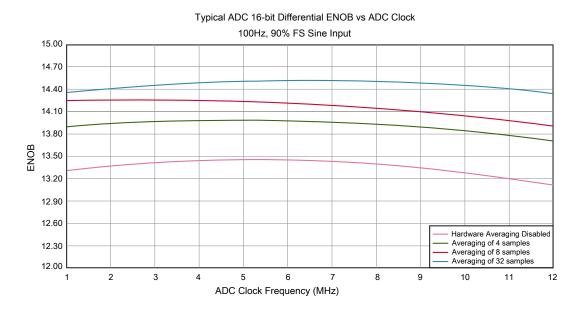


Figure 12. Typical ENOB vs. ADC_CLK for 16-bit differential mode

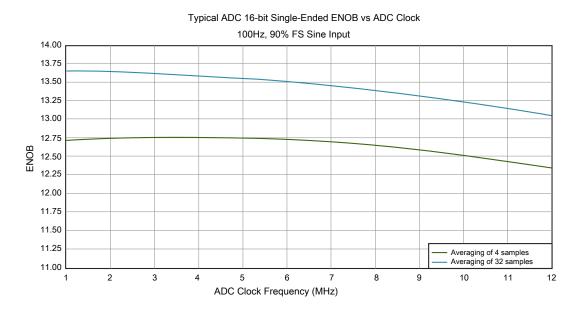


Figure 13. Typical ENOB vs. ADC_CLK for 16-bit single-ended mode

3.6.2 CMP and 6-bit DAC electrical specifications

Table 25. Comparator and 6-bit DAC electrical specifications

Symbol	Description	Min.	Тур.	Max.	Unit
V_{DD}	Supply voltage	1.71	_	3.6	V
I _{DDHS}	Supply current, high-speed mode (EN=1, PMODE=1)	_	_	200	μA
I _{DDLS}	Supply current, low-speed mode (EN=1, PMODE=0)	_	_	20	μΑ
V _{AIN}	Analog input voltage	V _{SS} - 0.3	_	V_{DD}	V
V _{AIO}	Analog input offset voltage	_	_	20	mV
V _H	Analog comparator hysteresis ¹				
	• CR0[HYSTCTR] = 00	_	5	_	mV
	• CR0[HYSTCTR] = 01	_	10	_	mV
	• CR0[HYSTCTR] = 10	_	20	_	mV
	• CR0[HYSTCTR] = 11	_	30	_	mV
V _{CMPOh}	Output high	V _{DD} - 0.5	_	_	V
V _{CMPOI}	Output low	_	_	0.5	V
t _{DHS}	Propagation delay, high-speed mode (EN=1, PMODE=1)	20	50	200	ns
t _{DLS}	Propagation delay, low-speed mode (EN=1, PMODE=0)	80	250	600	ns
	Analog comparator initialization delay ²	_	_	40	μs
I _{DAC6b}	6-bit DAC current adder (enabled)	_	7	_	μA
INL	6-bit DAC integral non-linearity	-0.5	_	0.5	LSB ³
DNL	6-bit DAC differential non-linearity	-0.3	_	0.3	LSB

^{1.} Typical hysteresis is measured with input voltage range limited to 0.6 to V_{DD} -0.6 V.

^{2.} Comparator initialization delay is defined as the time between software writes to change control inputs (Writes to CMP_DACCR[DACEN], CMP_DACCR[VRSEL], CMP_DACCR[VOSEL], CMP_MUXCR[PSEL], and CMP_MUXCR[MSEL]) and the comparator output settling to a stable level.

^{3.} $1 LSB = V_{reference}/64$

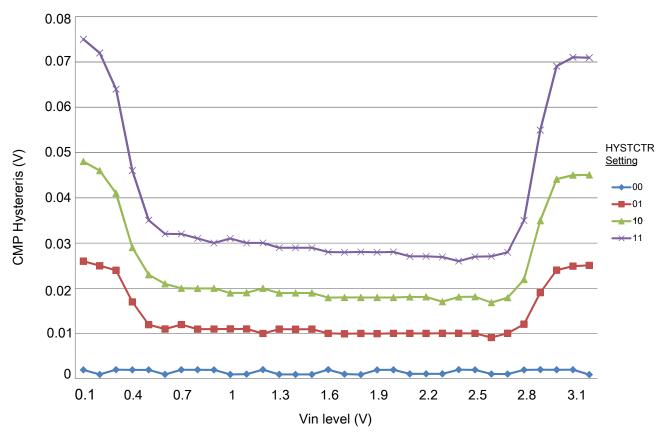


Figure 14. Typical hysteresis vs. Vin level (VDD = 3.3 V, PMODE = 0)

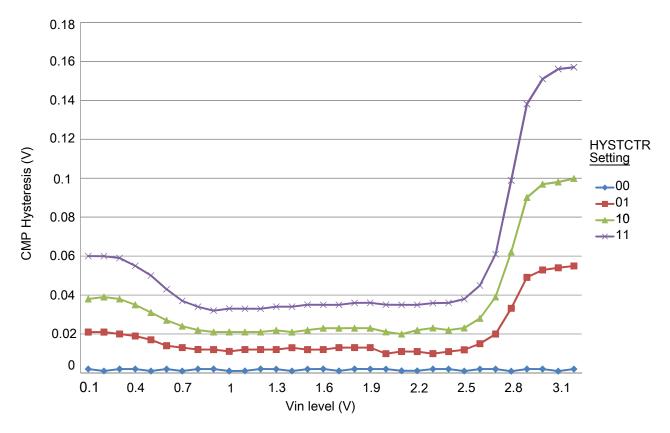


Figure 15. Typical hysteresis vs. Vin level (VDD = 3.3 V, PMODE = 1)

3.6.3 12-bit DAC electrical characteristics

3.6.3.1 12-bit DAC operating requirements Table 26. 12-bit DAC operating requirements

Symbol	Desciption	Min.	Max.	Unit	Notes
V_{DDA}	Supply voltage	1.71	3.6	V	
V _{DACR}	Reference voltage	1.13	3.6	V	1
C _L	Output load capacitance	_	100	pF	2
ΙL	Output load current	_	1	mA	

^{1.} The DAC reference can be selected to be V_{DDA} or V_{REF_OUT} .

^{2.} A small load capacitance (47 pF) can improve the bandwidth performance of the DAC.

3.6.3.2 12-bit DAC operating behaviors Table 27. 12-bit DAC operating behaviors

Symbol	Description	Min.	Тур.	Max.	Unit	Notes
I _{DDA_DACL}	Supply current — low-power mode	_	_	330	μΑ	
I _{DDA_DACH}	Supply current — high-speed mode	_	_	1200	μΑ	
t _{DACLP}	Full-scale settling time (0x080 to 0xF7F) — low-power mode	_	100	200	μs	1
t _{DACHP}	Full-scale settling time (0x080 to 0xF7F) — high-power mode	_	15	30	μs	1
t _{CCDACLP}	Code-to-code settling time (0xBF8 to 0xC08) — low-power mode and high-speed mode	_	0.7	1	μs	1
V _{dacoutl}	DAC output voltage range low — high- speed mode, no load, DAC set to 0x000	_	_	100	mV	
V _{dacouth}	DAC output voltage range high — high- speed mode, no load, DAC set to 0xFFF	V _{DACR} -100	_	V _{DACR}	mV	
INL	Integral non-linearity error — high speed mode	_	_	±8	LSB	2
DNL	Differential non-linearity error — V _{DACR} > 2 V	_	_	±1	LSB	3
DNL	Differential non-linearity error — V _{DACR} = VREF_OUT	_	_	±1	LSB	4
V _{OFFSET}	Offset error	_	±0.4	±0.8	%FSR	5
E _G	Gain error	_	±0.1	±0.6	%FSR	5
PSRR	Power supply rejection ratio, V _{DDA} ≥ 2.4 V	60	_	90	dB	
T _{CO}	Temperature coefficient offset voltage	_	3.7	_	μV/C	6
T_GE	Temperature coefficient gain error	_	0.000421	_	%FSR/C	
Rop	Output resistance (load = $3 \text{ k}\Omega$)	_	_	250	Ω	
SR	Slew rate -80h→ F7Fh→ 80h				V/µs	
	High power (SP _{HP})	1.2	1.7	_		
	Low power (SP _{LP})	0.05	0.12	_		
BW	3dB bandwidth				kHz	
	High power (SP _{HP})	550	_	_		
	Low power (SP _{LP})	40	_	_		

- 1. Settling within ±1 LSB
- 2. The INL is measured for 0 + 100 mV to V_{DACR} –100 mV
- 3. The DNL is measured for 0 + 100 mV to V_{DACR} -100 mV
- 4. The DNL is measured for 0 + 100 mV to V_{DACR} -100 mV with V_{DDA} > 2.4 V 5. Calculated by a best fit curve from V_{SS} + 100 mV to V_{DACR} 100 mV
- 6. $V_{DDA} = 3.0 \text{ V}$, reference select set for V_{DDA} (DACx_CO:DACRFS = 1), high power mode (DACx_CO:LPEN = 0), DAC set to 0x800, temperature range is across the full range of the device

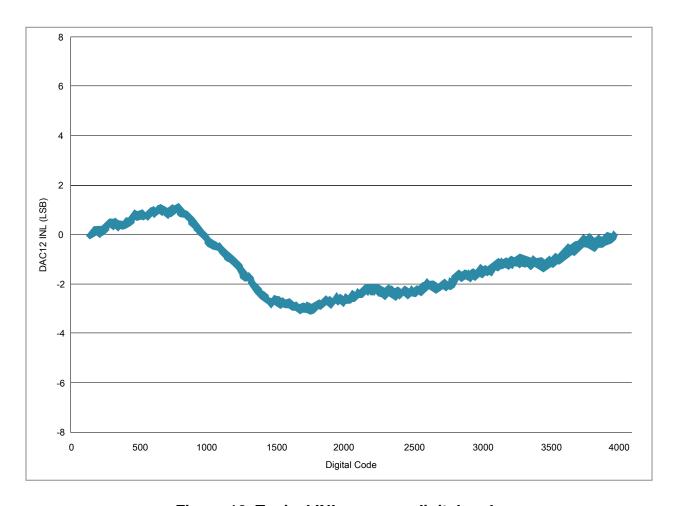


Figure 16. Typical INL error vs. digital code

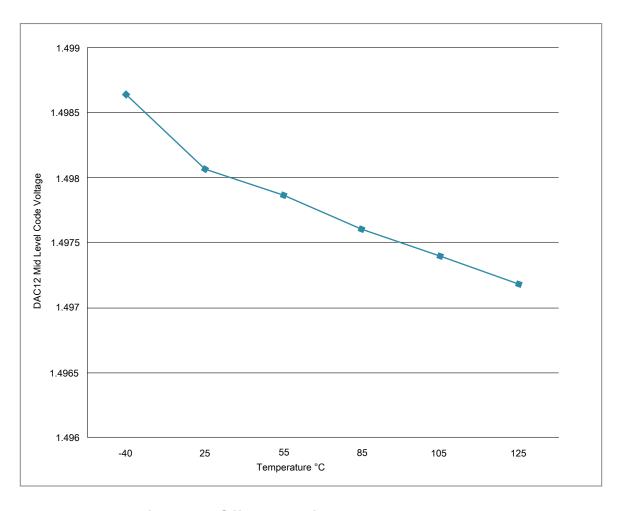


Figure 17. Offset at half scale vs. temperature

3.6.4 Voltage reference electrical specifications

Table 28. VREF full-range operating requirements

Symbol	Description	Min.	Max.	Unit	Notes
V_{DDA}	Supply voltage	1.71	3.6	V	
T _A	Temperature	Operating temperature range of the device		°C	
C _L	Output load capacitance	100		nF	1, 2

- 1. C_L must be connected to VREF_OUT if the VREF_OUT functionality is being used for either an internal or external reference.
- 2. The load capacitance should not exceed \pm -25% of the nominal specified C_L value over the operating temperature range of the device.

Table 29. VREF full-range operating behaviors

Symbol	Description	Min.	Тур.	Max.	Unit	Notes
V _{out}	Voltage reference output with factory trim at nominal V _{DDA} and temperature=25°C	1.1920	1.1950	1.1980	V	1
V _{out}	Voltage reference output with user trim at nominal V _{DDA} and temperature=25°C	1.1945	1.1950	1.1955	V	1
V _{step}	Voltage reference trim step	_	0.5	_	mV	1
V _{tdrift}	Temperature drift (Vmax -Vmin across the full temperature range)	_	_	15	mV	1
I _{bg}	Bandgap only current	_	_	80	μA	
I _{lp}	Low-power buffer current	_	_	360	uA	1
I _{hp}	High-power buffer current	_	_	1	mA	1
ΔV_{LOAD}	Load regulation				μV	1, 2
	• current = ± 1.0 mA	_	200	_		
T _{stup}	Buffer startup time	_	_	100	μs	
T _{chop_osc_st}	Internal bandgap start-up delay with chop oscillator enabled	_	_	35	ms	
V_{vdrift}	Voltage drift (Vmax -Vmin across the full voltage range)	_	2	_	mV	1

- 1. See the chip's Reference Manual for the appropriate settings of the VREF Status and Control register.
- 2. Load regulation voltage is the difference between the VREF_OUT voltage with no load vs. voltage with defined load

Table 30. VREF limited-range operating requirements

Symbol	Description	Min.	Max.	Unit	Notes
T _A	Temperature	0	70	°C	

Table 31. VREF limited-range operating behaviors

Symbol	Description	Min.	Max.	Unit	Notes
V _{tdrift}	Temperature drift (V _{max} -V _{min} across the limited temperature range)	_	10	mV	

3.7 Timers

See General switching specifications.

3.8 Communication interfaces

3.8.1 DSPI switching specifications (limited voltage range)

The Deserial Serial Peripheral Interface (DSPI) provides a synchronous serial bus with master and slave operations. Many of the transfer attributes are programmable. The tables below provide DSPI timing characteristics for classic SPI timing modes. Refer to the SPI chapter of the Reference Manual for information on the modified transfer formats used for communicating with slower peripheral devices.

Num	Description	Min.	Max.	Unit	Notes
	Operating voltage	2.7	3.6	V	
	Frequency of operation	_	25	MHz	
DS1	DSPI_SCK output cycle time	2 x t _{BUS}	_	ns	
DS2	DSPI_SCK output high/low time	(t _{SCK} /2) - 2	(t _{SCK} /2) + 2	ns	
DS3	DSPI_PCSn valid to DSPI_SCK delay	(t _{BUS} x 2) –	_	ns	1
DS4	DSPI_SCK to DSPI_PCSn invalid delay	(t _{BUS} x 2) –	_	ns	2
DS5	DSPI_SCK to DSPI_SOUT valid	_	8.5	ns	
DS6	DSPI_SCK to DSPI_SOUT invalid	-2	_	ns	
DS7	DSPI_SIN to DSPI_SCK input setup	16.2	_	ns	
DS8	DSPI_SCK to DSPI_SIN input hold	0	_	ns	

Table 32. Master mode DSPI timing (limited voltage range)

- 1. The delay is programmable in SPIx_CTARn[PSSCK] and SPIx_CTARn[CSSCK].
- 2. The delay is programmable in SPIx_CTARn[PASC] and SPIx_CTARn[ASC].

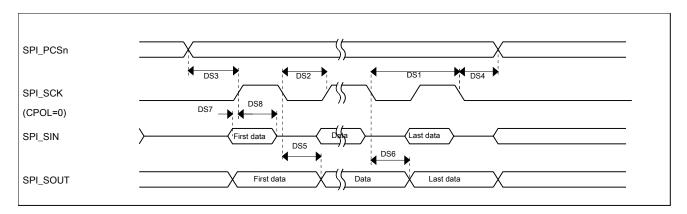


Figure 18. DSPI classic SPI timing — master mode

Table 33.	Slave mode DSF	I timing (limited	voltage range)
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Num	Description	Min.	Max.	Unit	Notes
	Operating voltage	2.7	3.6	V	
	Frequency of operation	_	12.5	MHz	1
DS9	DSPI_SCK input cycle time	4 x t _{BUS}	_	ns	
DS10	DSPI_SCK input high/low time	(t _{SCK} /2) - 2	$(t_{SCK}/2) + 2$	ns	
DS11	DSPI_SCK to DSPI_SOUT valid	_	21.4	ns	
DS12	DSPI_SCK to DSPI_SOUT invalid	0	_	ns	
DS13	DSPI_SIN to DSPI_SCK input setup	2.6	_	ns	
DS14	DSPI_SCK to DSPI_SIN input hold	7	_	ns	
DS15	DSPI_SS active to DSPI_SOUT driven	_	17	ns	
DS16	DSPI_SS inactive to DSPI_SOUT not driven	_	17	ns	

1. The maximum operating frequency is measured with noncontinuous CS and SCK. When DSPI is configured with continuous CS and SCK, the SPI clock must not be greater than 1/6 of the bus clock. For example, when the bus clock is 60 MHz, the SPI clock must not be greater than 10 MHz.

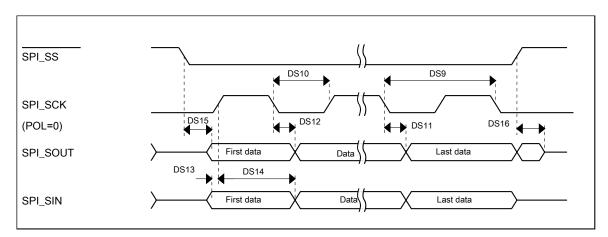


Figure 19. DSPI classic SPI timing — slave mode

3.8.2 DSPI switching specifications (full voltage range)

The Deserial Serial Peripheral Interface (DSPI) provides a synchronous serial bus with master and slave operations. Many of the transfer attributes are programmable. The tables below provides DSPI timing characteristics for classic SPI timing modes. Refer to the SPI chapter of the Reference Manual for information on the modified transfer formats used for communicating with slower peripheral devices.

Num	Description	Min.	Max.	Unit	Notes
	Operating voltage	1.71	3.6	V	1
	Frequency of operation	_	12.5	MHz	
DS1	DSPI_SCK output cycle time	4 x t _{BUS}	_	ns	
DS2	DSPI_SCK output high/low time	(t _{SCK} /2) - 4	(t _{SCK/2)} + 4	ns	
DS3	DSPI_PCSn valid to DSPI_SCK delay	(t _{BUS} x 2) – 4	_	ns	2
DS4	DSPI_SCK to DSPI_PCSn invalid delay	(t _{BUS} x 2) – 4	_	ns	3
DS5	DSPI_SCK to DSPI_SOUT valid	_	10	ns	
DS6	DSPI_SCK to DSPI_SOUT invalid	-4.5	_	ns	
DS7	DSPI_SIN to DSPI_SCK input setup	24.6	_	ns	
DS8	DSPI_SCK to DSPI_SIN input hold	0	_	ns	

Table 34. Master mode DSPI timing (full voltage range)

- 2. The delay is programmable in SPIx_CTARn[PSSCK] and SPIx_CTARn[CSSCK].
- 3. The delay is programmable in SPIx_CTARn[PASC] and SPIx_CTARn[ASC].

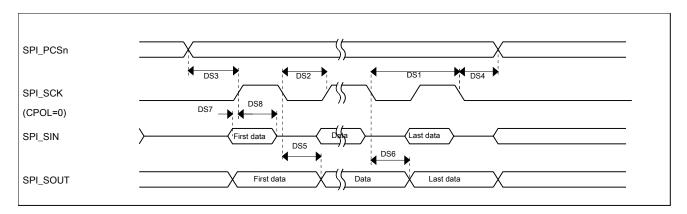


Figure 20. DSPI classic SPI timing — master mode

^{1.} The DSPI module can operate across the entire operating voltage for the processor, but to run across the full voltage range the maximum frequency of operation is reduced.

25

25

ns

ns

Num	Description	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
	Frequency of operation	_	6.25	MHz
DS9	DSPI_SCK input cycle time	8 x t _{BUS}	_	ns
DS10	DSPI_SCK input high/low time	(t _{SCK} /2) - 4	(t _{SCK/2)} + 4	ns
DS11	DSPI_SCK to DSPI_SOUT valid	_	29.5	ns
DS12	DSPI_SCK to DSPI_SOUT invalid	0	_	ns
DS13	DSPI_SIN to DSPI_SCK input setup	3.2	_	ns
DS14	DSPI_SCK to DSPI_SIN input hold	7	_	ns

Table 35. Slave mode DSPI timing (full voltage range)

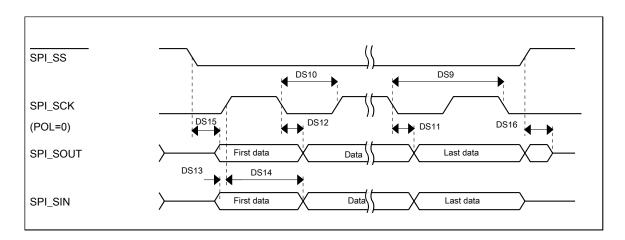


Figure 21. DSPI classic SPI timing — slave mode

3.8.3 Inter-Integrated Circuit Interface (I²C) timing Table 36. I ²C timing

DSPI_SS active to DSPI_SOUT driven

DSPI_SS inactive to DSPI_SOUT not driven

DS15

DS16

Characteristic	Symbol	Standard Mode		Fast Mode		Unit
		Minimum	Maximum	Minimum	Maximum	
SCL Clock Frequency	f _{SCL}	0	100	0	400 ¹	kHz
Hold time (repeated) START condition. After this period, the first clock pulse is generated.	t _{HD} ; STA	4	_	0.6	_	μs
LOW period of the SCL clock	t _{LOW}	4.7	_	1.25	_	μs
HIGH period of the SCL clock	t _{HIGH}	4	_	0.6	_	μs
Set-up time for a repeated START condition	t _{SU} ; STA	4.7	_	0.6	_	μs

Table 36.	I ² C timing	(continued)
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Characteristic	Symbol	Standard Mode		Fast	Unit	
		Minimum	Maximum	Minimum	Maximum	
Data hold time for I ² C bus devices	t _{HD} ; DAT	0 ²	3.45 ³	04	0.9 ²	μs
Data set-up time	t _{SU} ; DAT	250 ⁵	_	100 ^{3, 6}	_	ns
Rise time of SDA and SCL signals	t _r	_	1000	20 +0.1C _b ⁷	300	ns
Fall time of SDA and SCL signals	t _f	_	300	20 +0.1C _b ⁶	300	ns
Set-up time for STOP condition	t _{SU} ; STO	4	_	0.6	_	μs
Bus free time between STOP and START condition	t _{BUF}	4.7	_	1.3	_	μs
Pulse width of spikes that must be suppressed by the input filter	t _{SP}	N/A	N/A	0	50	ns

- 1. The maximum SCL Clock Frequency in Fast mode with maximum bus loading can only be achieved when using the High drive pins across the full voltage range and when using the Normal drive pins and VDD ≥ 2.7 V.
- The master mode I²C deasserts ACK of an address byte simultaneously with the falling edge of SCL. If no slaves
 acknowledge this address byte, then a negative hold time can result, depending on the edge rates of the SDA and SCL
 lines.
- 3. The maximum tHD; DAT must be met only if the device does not stretch the LOW period (tLOW) of the SCL signal.
- 4. Input signal Slew = 10 ns and Output Load = 50 pF
- 5. Set-up time in slave-transmitter mode is 1 IPBus clock period, if the TX FIFO is empty.
- 6. A Fast mode I^2C bus device can be used in a Standard mode I^2C bus system, but the requirement $t_{SU; DAT} \ge 250$ ns must then be met. This is automatically the case if the device does not stretch the LOW period of the SCL signal. If such a device does stretch the LOW period of the SCL signal, then it must output the next data bit to the SDA line $t_{rmax} + t_{SU; DAT} = 1000 + 250 = 1250$ ns (according to the Standard mode I^2C bus specification) before the SCL line is released.
- 7. $C_b = \text{total capacitance of the one bus line in pF}$.

Table 37. I²C 1 Mbps timing

Characteristic	Symbol	Minimum	Maximum	Unit
SCL Clock Frequency	f _{SCL}	0	1 ¹	MHz
Hold time (repeated) START condition. After this period, the first clock pulse is generated.	t _{HD} ; STA	0.26	_	μs
LOW period of the SCL clock	t _{LOW}	0.5	_	μs
HIGH period of the SCL clock	t _{HIGH}	0.26	_	μs
Set-up time for a repeated START condition	t _{SU} ; STA	0.26	_	μs
Data hold time for I ₂ C bus devices	t _{HD} ; DAT	0	_	μs
Data set-up time	t _{SU} ; DAT	50	_	ns
Rise time of SDA and SCL signals	t _r	20 +0.1C _b , ²	120	ns
Fall time of SDA and SCL signals	t _f	20 +0.1C _b ²	120	ns
Set-up time for STOP condition	t _{SU} ; STO	0.26	_	μs
Bus free time between STOP and START condition	t _{BUF}	0.5	_	μs
Pulse width of spikes that must be suppressed by the input filter	t _{SP}	0	50	ns

^{1.} The maximum SCL clock frequency of 1 Mbps can support maximum bus loading when using the High drive pins across the full voltage range.

^{2.} $C_b = total$ capacitance of the one bus line in pF.

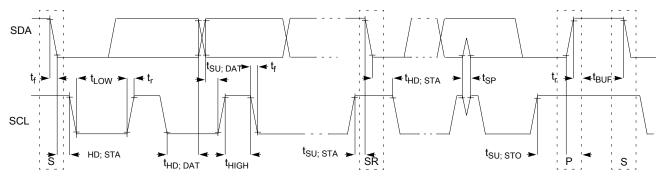


Figure 22. Timing definition for devices on the I²C bus

3.8.4 UART switching specifications

See General switching specifications.

4 Dimensions

4.1 Obtaining package dimensions

Package dimensions are provided in package drawings.

To find a package drawing, go to nxp.com and perform a keyword search for the drawing's document number:

If you want the drawing for this package	Then use this document number
32-pin QFN	98ARE10566D
48-pin LQFP	98ASH00962A
64-pin LQFP	98ASS23234W

5 Pinout

5.1 KV30F Signal Multiplexing and Pin Assignments

The signal multiplexing and pin assignments are also provided in an Excel file attached to this document:

1. Click the paperclip symbol on the left side of the PDF window.

- 2. Double-click on the Excel file to open it.
- 3. Select the "Pinout" tab.

The Port Control Module is responsible for selecting which ALT functionality is available on each pin.

5.2 KV30F Signal Multiplexing and Pin Assignments

The following table shows the signals available on each pin and the locations of these pins on the devices supported by this document. The Port Control Module is responsible for selecting which ALT functionality is available on each pin.

64 LQFP	48 LQFP	32 QFN	Pin Name	Default	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7
1	_	-	PTE0/ CLKOUT32K	ADC1_SE4a	ADC1_SE4a	PTE0/ CLKOUT32K		UART1_TX				
2	ı	1	PTE1/ LLWU_P0	ADC1_SE5a	ADC1_SE5a	PTE1/ LLWU_P0		UART1_RX				
3	1	1	VDD	VDD	VDD							
4	2	2	VSS	VSS	VSS							
5	3	3	PTE16	ADC0_SE4a/ ADC0_DP1/ ADC1_DP2	ADC0_SE4a/ ADC0_DP1/ ADC1_DP2	PTE16	SPI0_PCS0	UART1_TX	FTM_CLKIN0		FTM0_FLT3	
6	4	4	PTE17	ADC0_SE5a/ ADC0_DM1/ ADC1_DM2	ADC0_SE5a/ ADC0_DM1/ ADC1_DM2	PTE17	SPI0_SCK	UART1_RX	FTM_CLKIN1		LPTMR0_ ALT3	
7	5	5	PTE18	ADC0_SE6a/ ADC1_DP1/ ADC0_DP2	ADC0_SE6a/ ADC1_DP1/ ADC0_DP2	PTE18	SPI0_SOUT	UART1_CTS_ b	I2C0_SDA			
8	6	6	PTE19	ADC0_SE7a/ ADC1_DM1/ ADC0_DM2	ADC0_SE7a/ ADC1_DM1/ ADC0_DM2	PTE19	SPI0_SIN	UART1_RTS_ b	I2C0_SCL			
9	7	-	ADC0_DP0/ ADC1_DP3	ADC0_DP0/ ADC1_DP3	ADC0_DP0/ ADC1_DP3							
10	8	-	ADC0_DM0/ ADC1_DM3	ADC0_DM0/ ADC1_DM3	ADC0_DM0/ ADC1_DM3							
11	-	-	ADC1_DP0/ ADC0_DP3	ADC1_DP0/ ADC0_DP3	ADC1_DP0/ ADC0_DP3							
12	_	1	ADC1_DM0/ ADC0_DM3	ADC1_DM0/ ADC0_DM3	ADC1_DM0/ ADC0_DM3							
13	9	7	VDDA	VDDA	VDDA							
14	10	7	VREFH	VREFH	VREFH							
15	11	8	VREFL	VREFL	VREFL							
16	12	8	VSSA	VSSA	VSSA							

64 LQFP	48 LQFP	32 QFN	Pin Name	Default	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7
17	13	_	VREF_OUT/ CMP1_IN5/ CMP0_IN5/ ADC1_SE18	VREF_OUT/ CMP1_IN5/ CMP0_IN5/ ADC1_SE18	VREF_OUT/ CMP1_IN5/ CMP0_IN5/ ADC1_SE18							
18	14	9	DACO_OUT/ CMP1_IN3/ ADCO_SE23	DAC0_OUT/ CMP1_IN3/ ADC0_SE23	DACO_OUT/ CMP1_IN3/ ADCO_SE23							
19	-	-	CMP0_IN4/ ADC1_SE23	CMP0_IN4/ ADC1_SE23	CMP0_IN4/ ADC1_SE23							
20	15	10	PTE24	ADC0_SE17	ADC0_SE17	PTE24		FTM0_CH0		I2C0_SCL	EWM_OUT_b	
21	16	11	PTE25	ADC0_SE18	ADC0_SE18	PTE25		FTM0_CH1		I2C0_SDA	EWM_IN	
22	17	12	PTA0	JTAG_TCLK/ SWD_CLK		PTA0	UARTO_CTS_ b	FTM0_CH5		EWM_IN		JTAG_TCLK/ SWD_CLK
23	18	13	PTA1	JTAG_TDI		PTA1	UARTO_RX	FTM2_CH0	CMP0_OUT	FTM2_QD_ PHA	FTM1_CH1	JTAG_TDI
24	19	14	PTA2	JTAG_TDO/ TRACE_SWO		PTA2	UART0_TX	FTM2_CH1	CMP1_OUT	FTM2_QD_ PHB	FTM1_CH0	JTAG_TDO/ TRACE_SWO
25	20	15	PTA3	JTAG_TMS/ SWD_DIO		PTA3	UARTO_RTS_ b	FTM0_CH0	FTM2_FLT0	EWM_OUT_b		JTAG_TMS/ SWD_DIO
26	21	16	PTA4/ LLWU_P3	NMI_b		PTA4/ LLWU_P3		FTM0_CH1		FTM0_FLT3		NMI_b
27	1	-	PTA5	DISABLED		PTA5		FTM0_CH2				JTAG_TRST_ b
28	-	-	PTA12	DISABLED		PTA12		FTM1_CH0				FTM1_QD_ PHA
29	1	1	PTA13/ LLWU_P4	DISABLED		PTA13/ LLWU_P4		FTM1_CH1				FTM1_QD_ PHB
30	22	-	VDD	VDD	VDD							
31	23	1	VSS	VSS	VSS							
32	24	17	PTA18	EXTAL0	EXTAL0	PTA18		FTM0_FLT2	FTM_CLKIN0			
33	25	18	PTA19	XTAL0	XTAL0	PTA19	FTM0_FLT0	FTM1_FLT0	FTM_CLKIN1		LPTMR0_ ALT1	
34	26	19	RESET_b	RESET_b	RESET_b							
35	27	20	PTB0/ LLWU_P5	ADC0_SE8/ ADC1_SE8	ADC0_SE8/ ADC1_SE8	PTB0/ LLWU_P5	12C0_SCL	FTM1_CH0			FTM1_QD_ PHA	UARTO_RX
36	28	21	PTB1	ADC0_SE9/ ADC1_SE9	ADC0_SE9/ ADC1_SE9	PTB1	I2C0_SDA	FTM1_CH1	FTM0_FLT2	EWM_IN	FTM1_QD_ PHB	UARTO_TX
37	29	-	PTB2	ADC0_SE12	ADC0_SE12	PTB2	I2C0_SCL	UARTO_RTS_ b	FTM0_FLT1		FTM0_FLT3	
38	30	-	PTB3	ADC0_SE13	ADC0_SE13	PTB3	I2C0_SDA	UARTO_CTS_ b			FTM0_FLT0	
39	31	_	PTB16	DISABLED		PTB16		UARTO_RX	FTM_CLKIN0		EWM_IN	
40	32	-	PTB17	DISABLED		PTB17		UART0_TX	FTM_CLKIN1		EWM_OUT_b	
41	_	_	PTB18	DISABLED		PTB18		FTM2_CH0			FTM2_QD_ PHA	

Pinout

64 LQFP	48 LQFP	32 QFN	Pin Name	Default	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7
42	-	_	PTB19	DISABLED		PTB19		FTM2_CH1			FTM2_QD_ PHB	
43	33	-	PTC0	ADC0_SE14	ADC0_SE14	PTC0	SPI0_PCS4	PDB0_ EXTRG		CMP0_OUT	FTM0_FLT1	SPI0_PCS0
44	34	22	PTC1/ LLWU_P6	ADC0_SE15	ADC0_SE15	PTC1/ LLWU_P6	SPI0_PCS3	UART1_RTS_ b	FTM0_CH0	FTM2_CH0		
45	35	23	PTC2	ADC0_SE4b/ CMP1_IN0	ADC0_SE4b/ CMP1_IN0	PTC2	SPI0_PCS2	UART1_CTS_ b	FTM0_CH1	FTM2_CH1		
46	36	24	PTC3/ LLWU_P7	CMP1_IN1	CMP1_IN1	PTC3/ LLWU_P7	SPI0_PCS1	UART1_RX	FTM0_CH2	CLKOUT		
47	-	_	VSS	VSS	VSS							
48	_	_	VDD	VDD	VDD							
49	37	25	PTC4/ LLWU_P8	DISABLED		PTC4/ LLWU_P8	SPI0_PCS0	UART1_TX	FTM0_CH3		CMP1_OUT	
50	38	26	PTC5/ LLWU_P9	DISABLED		PTC5/ LLWU_P9	SPI0_SCK	LPTMR0_ ALT2			CMP0_OUT	FTM0_CH2
51	39	27	PTC6/ LLWU_P10	CMP0_IN0	CMP0_IN0	PTC6/ LLWU_P10	SPI0_SOUT	PDB0_ EXTRG		UARTO_RX		I2C0_SCL
52	40	28	PTC7	CMP0_IN1	CMP0_IN1	PTC7	SPI0_SIN			UARTO_TX		I2C0_SDA
53	-	1	PTC8	ADC1_SE4b/ CMP0_IN2	ADC1_SE4b/ CMP0_IN2	PTC8						
54	-	-	PTC9	ADC1_SE5b/ CMP0_IN3	ADC1_SE5b/ CMP0_IN3	PTC9					FTM2_FLT0	
55	_	_	PTC10	ADC1_SE6b	ADC1_SE6b	PTC10						
56	-	-	PTC11/ LLWU_P11	ADC1_SE7b	ADC1_SE7b	PTC11/ LLWU_P11						
57	41	1	PTD0/ LLWU_P12	DISABLED		PTD0/ LLWU_P12	SPI0_PCS0	UARTO_RTS_ b	FTM0_CH0	UART1_RX		
58	42	-	PTD1	ADC0_SE5b	ADC0_SE5b	PTD1	SPI0_SCK	UARTO_CTS_	FTM0_CH1	UART1_TX		
59	43	-	PTD2/ LLWU_P13	DISABLED		PTD2/ LLWU_P13	SPI0_SOUT	UARTO_RX	FTM0_CH2			I2C0_SCL
60	44	-	PTD3	DISABLED		PTD3	SPI0_SIN	UARTO_TX	FTM0_CH3			I2C0_SDA
61	45	29	PTD4/ LLWU_P14	DISABLED		PTD4/ LLWU_P14	SPI0_PCS1	UARTO_RTS_ b	FTM0_CH4	FTM2_CH0	EWM_IN	
62	46	30	PTD5	ADC0_SE6b	ADC0_SE6b	PTD5	SPI0_PCS2	UARTO_CTS_	FTM0_CH5	FTM2_CH1	EWM_OUT_b	
63	47	31	PTD6/ LLWU_P15	ADC0_SE7b	ADC0_SE7b	PTD6/ LLWU_P15	SPI0_PCS3	UARTO_RX	FTM0_CH0	FTM1_CH0	FTM0_FLT0	
64	48	32	PTD7	DISABLED		PTD7		UARTO_TX	FTM0_CH1	FTM1_CH1	FTM0_FLT1	

5.3 Recommended connection for unused analog and digital pins

The following table shows the recommended connections for analog interface pins if those analog interfaces are not used in the customer's application.

Table 38. Recommended connection for unused analog interfaces

Pin Type		Short recommendation	Detailed recommendation
Analog/non GPIO	PGAx/ADCx	Float	Analog input - Float
Analog/non GPIO	ADCx/CMPx	Float	Analog input - Float
Analog/non GPIO	VREF_OUT	Float	Analog output - Float
Analog/non GPIO	DACx_OUT	Float	Analog output - Float
Analog/non GPIO	RTC_WAKEUP_B	Float	Analog output - Float
Analog/non GPIO	XTAL32	Float	Analog output - Float
Analog/non GPIO	EXTAL32	Float	Analog input - Float
GPIO/Analog	PTA18/EXTAL0	Float	Analog input - Float
GPIO/Analog	PTA19/XTAL0	Float	Analog output - Float
GPIO/Analog	PTx/ADCx	Float	Float (default is analog input)
GPIO/Analog	PTx/CMPx	Float	Float (default is analog input)
GPIO/Digital	PTA0/JTAG_TCLK	Float	Float (default is JTAG with pulldown)
GPIO/Digital	PTA1/JTAG_TDI	Float	Float (default is JTAG with pullup)
GPIO/Digital	PTA2/JTAG_TDO	Float	Float (default is JTAG with pullup)
GPIO/Digital	PTA3/JTAG_TMS	Float	Float (default is JTAG with pullup)
GPIO/Digital	PTA4/NMI_b	10k Ω pullup or disable and float	Pull high or disable in PCR & FOPT and float
GPIO/Digital	РТх	Float	Float (default is disabled)
VDDA	VDDA	Always connect to VDD potential	Always connect to VDD potential
VREFH	VREFH	Always connect to VDD potential	Always connect to VDD potential
VREFL	VREFL	Always connect to VSS potential	Always connect to VSS potential
VSSA	VSSA	Always connect to VSS potential	Always connect to VSS potential

5.4 KV30F Pinouts

The pinout diagrams are also provided in an Excel file attached to this document:

Pinout

- 1. Click the paperclip symbol on the left side of the PDF window.
- 2. Double-click on the Excel file to open it.
- 3. Select the respective package tab.

Many signals may be multiplexed onto a single pin. To determine what signals can be used on which pin, see the previous section.

5.5 KV30F Pinouts

The below figure shows the pinout diagram for the devices supported by this document. Many signals may be multiplexed onto a single pin. To determine what signals can be used on which pin, see the previous section.

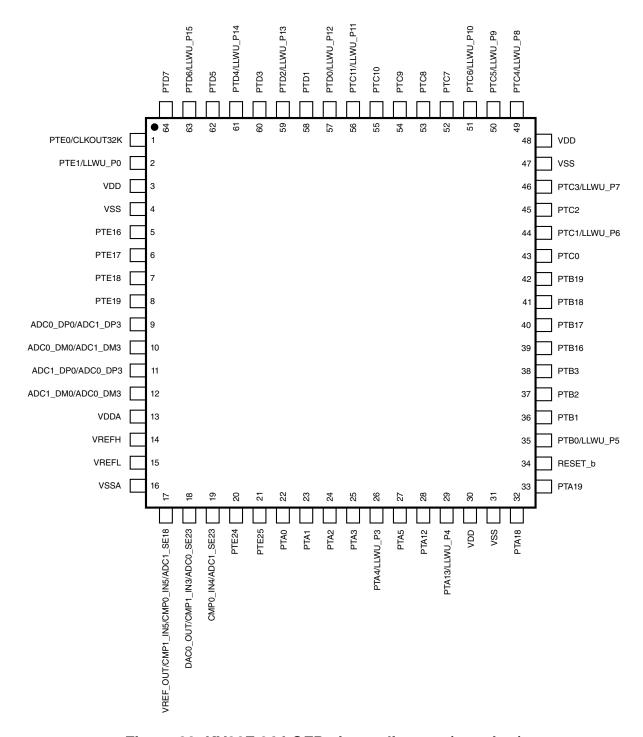


Figure 23. KV30F 64 LQFP pinout diagram (top view)

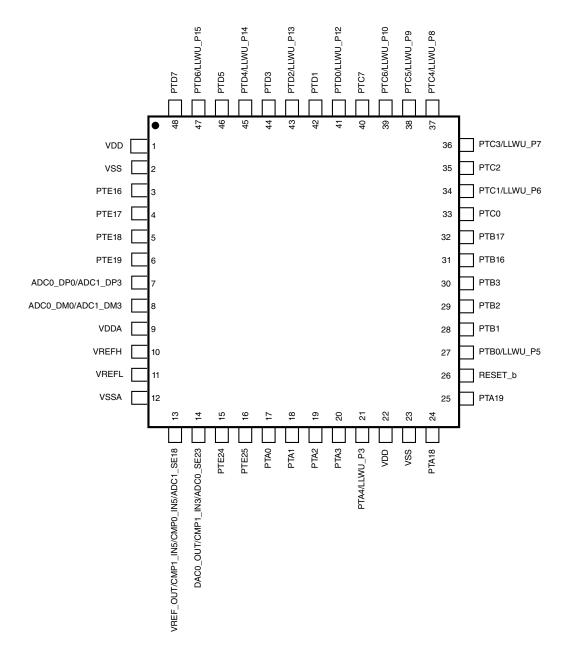


Figure 24. KV30F 48 LQFP pinout diagram

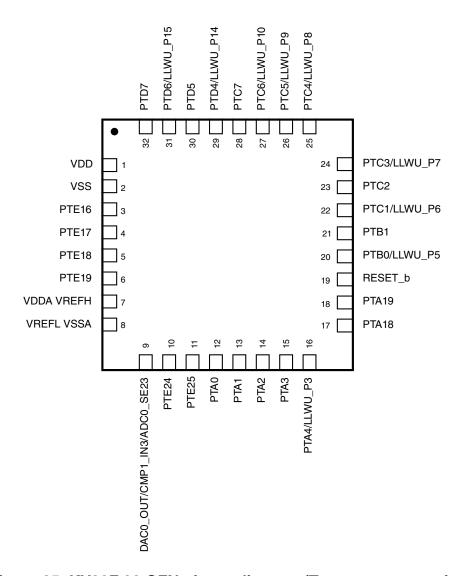


Figure 25. KV30F 32 QFN pinout diagram (Transparent top view)

6 Part identification

6.1 Description

Part numbers for the chip have fields that identify the specific part. You can use the values of these fields to determine the specific part you have received.

6.2 Format

Part numbers for this device have the following format:

Q KV## A FFF R T PP CC S N

6.3 Fields

This table lists the possible values for each field in the part number (not all combinations are valid):

Field	Description	Values
Q	Qualification status	 M = Fully qualified, general market flow P = Prequalification
KV##	Kinetis V Series	KV3x: Cortex-M4 based MCU
А	Key attribute	 D = Cortex-M4 w/ DSP F = Cortex-M4 w/ DSP and FPU
FFF	Program flash memory size	 64 = 64 KB 128 = 128 KB 256 = 256 KB 512 = 512 KB
R	Silicon revision	(Blank) = MainA = Revision after main
Т	Temperature range (°C)	 V = -40 to 105 C = -40 to 85
PP	Package identifier	 FM = 32 QFN (5 mm x 5 mm) LF = 48 LQFP (7 mm x 7 mm) LH = 64 LQFP (10 mm x 10 mm) LL = 100 LQFP (14 mm x 14 mm) MC = 121 XFBGA (8 mm x 8 mm) DC = 121 XFBGA (8 mm x 8 mm x 0.5 mm)
CC	Maximum CPU frequency (MHz)	10 = 100 MHz12 = 120 MHz
S	Software type	(Blank) = Not software enabled
N	Packaging type	R = Tape and reel (Blank) = Trays

6.4 Example

This is an example part number:

MKV30F128VLH10

6.5 Package Markings

Package markings for Kinetis MCU devices consists of 3 sets of identifiers:

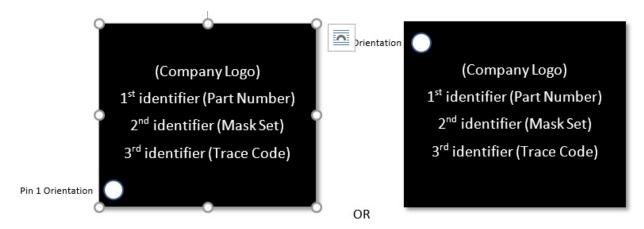


Figure 26. Package Marking

1st identifier defines the Part Number and is composed of at least 6 characters typically represented as one line. Part Number may wrap around to a second line if the package markings have 4 lines total.

2nd identifier defines the Mask Set and is composed of 5 characters.

3rd identifier defines the Trace Code used for traceability data and the Date Code for the week of manufacture is a subset of the standard 10 character format

- The standard trace code format is "xxxxYYWWx":
 - The four leading digits and last one represented by an "x" can be ignored and "YYWW" indicate the Date Code
 - "YY" represents the last 2 digits of the calendar year (e.g. 18 corresponds to the year 2018)
 - "WW" represents the work week within the calendar year (e.g. 50 corresponds to week 50)
- If the Trace Code on your device consists of less than 10 characters or the package markings are different than what has outlined above, please contact your local NXP representative for further details

7 Terminology and guidelines

7.1 Definitions

Key terms are defined in the following table:

Term	Definition
Rating	A minimum or maximum value of a technical characteristic that, if exceeded, may cause permanent chip failure:
	 Operating ratings apply during operation of the chip. Handling ratings apply when the chip is not powered.
	NOTE: The likelihood of permanent chip failure increases rapidly as soon as a characteristic begins to exceed one of its operating ratings.
Operating requirement	A specified value or range of values for a technical characteristic that you must guarantee during operation to avoid incorrect operation and possibly decreasing the useful life of the chip
Operating behavior	A specified value or range of values for a technical characteristic that are guaranteed during operation if you meet the operating requirements and any other specified conditions
Typical value	A specified value for a technical characteristic that:
	 Lies within the range of values specified by the operating behavior Is representative of that characteristic during operation when you meet the typical-value conditions or other specified conditions
	NOTE: Typical values are provided as design guidelines and are neither tested nor guaranteed.

7.2 Examples

Operating rating:

Symbol	Description	Min.	Max.	Unit
V _{DD}	1.0 V core supply voltage	-0.3 LRW	1.2	٧

Operating requirement:

Symbol	Description	Min.	Max.	Unit
V_{DD}	1.0 V core supply voltage	0.9	1.1	V

Operating behavior that includes a typical value:

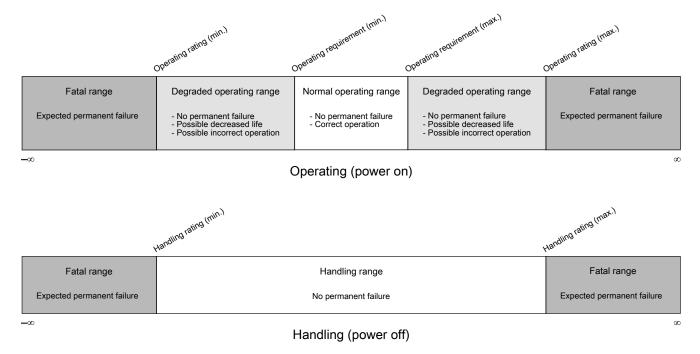
Symbol	Description	Min.	Тур.	Max.	Unit
I _{WP}	Digital I/O weak pullup/pulldown current	10 tank	70	130	μΑ

7.3 Typical-value conditions

Typical values assume you meet the following conditions (or other conditions as specified):

Symbol	Description	Value	Unit
T _A	Ambient temperature	25	°C
V_{DD}	Supply voltage	3.3	V

7.4 Relationship between ratings and operating requirements



7.5 Guidelines for ratings and operating requirements

Follow these guidelines for ratings and operating requirements:

- Never exceed any of the chip's ratings.
- During normal operation, don't exceed any of the chip's operating requirements.
- If you must exceed an operating requirement at times other than during normal operation (for example, during power sequencing), limit the duration as much as possible.

8 Revision History

The following table provides a revision history for this document.

Table 39. Revision History

Rev. No.	Date	Substantial Changes
6	03/2021	 Updated ARM to Arm as per Arm branding guidelines Updated Part Number Marking of MKV30F128VLF10 from M30J6V to M30J7V in Ordering Information table
5	06/2020	 Added Device Revision Number Table Updated Voltage and current operating ratings

Table 39. Revision History (continued)

Rev. No.	Date	Substantial Changes
		 Added VBAT:SR_{PWR} in Voltage and current operating requirements Updated Ordering information table in Front Matter by adding Part number marking and packages column Added generic Package Markings section Updated footnote attached to Reference Voltage in 12-bit DAC operating requirements Removed references to KMS content
4	08/2016	 In "Power consumption operating behaviors" table, added "Low power mode peripheral adders—typical value" table In "Thermal operating requirements" table, in footnote, corrected "T_J = T_A + Θ_{JA}" to "T_J = T_A + R_{ΘJA}" In "Slave mode DSPI timing (limited voltage range)" table, added footnote regarding maximum frequency of operation Added new section, "Recommended connections for unused analog and digital pins" Updated "NVM program/erase timing specifications" table; updated values for t_{hversall} (Erase All high-voltage time) Added Terminology and Guidelines section Updated Thermal Attributes value for 48LQFP Added Device Revision Number table in front matter Added KMS related information in front matter Added Kinetis Motor Suite section Added "S" in Format and Part Identification table Updated the Part Number Example Deleted Package Your Way footnote attached to 48 LQFP
3	4/2015	 Throughout: Modified notes related to 48-pin LQFP to say, "The 48-pin LQFP package for this product is not yet available; however, it is included in a Package Your Way program for Kinetis MCUs. Please visit www.Freescale.com/KPYW for more details." On page 1: Under "Clocks," corrected second and third bullets—moved "with FLL" from "internal oscillators" to "multipurpose clock generator" bullet Under "Communication interfaces," updated I²C bullet to indicate support for up to 1 Mbps operation Under "Operating characteristics," specified that voltage range includes flash writes In "Voltage and current operating requirements" table: Removed content related to positive injection Updated footnote 1 to say that all analog and I/O pins are internally clamped to V_{SS} only (not V_{SS} and V_{DD})through ESD protection diodes. In "Power mode transition operating behaviors" table, removed rows for LLS2 and LLS3 In "Power consumption operating behaviors" table: Provided additional temperature data Added Max IDD values based on characterization results equivalent to mean + 3 sigma Removed rows for LLS2 and LLS3 Updated "EMC radiated emissions operating behaviors" table In "Thermal operating requirements" table, added the following footnote for ambient temperature: "Maximum T_A can be exceeded only if the user ensures that T_J does not exceed maximum T_J. The simplest method to determine T_J is: T_J = T_A + Θ_{JA} x chip power dissipation" Updated "IRC48M Specifications":

Table 39. Revision History (continued)

voltage range and when using the Normal drive pins and VDD ≥ 2.7 V." • Updated minimum Fast mode value for LOW period of the SCL clock to 1.25 μ • Added "l²C 1 Mbps timing" table • Removed Section 6, "Ordering parts." • Added "48-pin LQFP part marking" section • Added "32-pin QFN part marking" section • Added "32-pin QFN part marking" section • On p. 1, under "Memories and memory interfaces," added bullet, "Preprogrammed Kinetis flashloader for one-time, in-system factory programming" • On p. 1, added parenthetical element to the following bullet under "Analog modules". *Accurate internal voltage reference (not available for 32-pin QFN package) • In "Voltage and current operating ratings" section, updated digital supply current maximum value • In "Voltage and current operating behaviors" section, updated input leakage information • In "Power consumption operating behaviors table": • Updated existing typical and maximum power measurements • Added new typical power measurements for the following: • IDD_HSRUN (High Speed Run mode, all peripheral clocks disabled, current executing CoreMark code) • IDD_HSRUN (High Speed Run mode, all peripheral clocks disabled, current executing while(1) loop) • IDD_RUN (Run mode current in Compute operation, all peripheral clocks disabled, executing CoreMark code) • IDD_RUN (Run mode current in Compute operation, all peripheral clocks disabled, executing while(1) loop) • IDD_VLPR (Very Low Power mode current in Compute operation, all peripheral clocks disabled, executing CoreMark code)	Rev. No.	Date	Substantial Changes
Kinetis flashloader for one-time, in-system factory programming" On p. 1, added parenthetical element to the following bullet under "Analog modules": Accurate internal voltage reference (not available for 32-pin QFN package) In "Voltage and current operating ratings" section, updated digital supply current maximum value In "Voltage and current operating behaviors" section, updated input leakage information In "Power consumption operating behaviors table": Updated existing typical and maximum power measurements Added new typical power measurements for the following: IDD_HSRUN (High Speed Run mode, all peripheral clocks disabled, current executing CoreMark code) IDD_HSRUN (High Speed Run mode, all peripheral clocks disabled, current executing While(1) loop) IDD_RUN (Run mode current in Compute operation, all peripheral clocks disabled, executing CoreMark code) IDD_RUN (Run mode current in Compute operation, all peripheral clocks disabled, executing while(1) loop) IDD_VLPR (Very Low Power mode current in Compute operation, all peripheral clocks disabled, executing CoreMark code) IDD_VLPR (Very Low Power Run mode current in Compute operation, all peripheral clocks disabled, executing while(1) loop) Updated section, "EMC radiated emissions operating behaviors for 64 LQFP package" In "Thermal attributes" section, added 64-pin LQFP and 32-pin QFN package values Updated "MCG specifications" table Updated "VREF full-range operating behaviors" table In the "Part identification" section, added "Format" and "Fields" subsections			 Added specifications for Δ_{firc48m_hv} (-40°C to 85°C) In "I²C timing" table, Added the following footnote on maximum Fast mode value for SCL Clock Frequency: "The maximum SCL Clock Frequency in Fast mode with maximum bus loading can only be achieved when using the High drive pins across the full voltage range and when using the Normal drive pins and VDD ≥ 2.7 V." Updated minimum Fast mode value for LOW period of the SCL clock to 1.25 μ Added "I²C 1 Mbps timing" table Removed Section 6, "Ordering parts." Added "48-pin LQFP part marking" section
	2	8/2014	On p. 1, under "Memories and memory interfaces," added bullet, "Preprogrammed Kinetis flashloader for one-time, in-system factory programming" On p. 1, added parenthetical element to the following bullet under "Analog modules": Accurate internal voltage reference (not available for 32-pin QFN package) In "Voltage and current operating ratings" section, updated digital supply current maximum value In "Voltage and current operating behaviors" section, updated input leakage information In "Power consumption operating behaviors table": Updated existing typical and maximum power measurements Added new typical power measurements for the following: IDD_HSRUN (High Speed Run mode, all peripheral clocks disabled, current executing CoreMark code) IDD_HSRUN (High Speed Run mode, all peripheral clocks disabled, current executing while(1) loop) IDD_RUN (Run mode current in Compute operation, all peripheral clocks disabled, executing CoreMark code) IDD_RUN (Run mode current in Compute operation, all peripheral clocks disabled, executing while(1) loop) IDD_VLPR (Very Low Power mode current in Compute operation, all peripheral clocks disabled, executing CoreMark code) IDD_VLPR (Very Low Power Run mode current in Compute operation, all peripheral clocks disabled, executing while(1) loop) Updated section, "EMC radiated emissions operating behaviors for 64 LQFP package" In "Thermal attributes" section, added 64-pin LQFP and 32-pin QFN package values Updated "MCG specifications" table Updated "VREF full-range operating behaviors" table
	1	3/2014	

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